# DLP650LNIR 0.65 NIR WXGA S450 DMD

## 1 特長

- 100万を超えるマイクロミラーによる1280×800 (WXGA)アレイ
  - マイクロミラー・ピッチ: 10.8µm
  - マイクロミラー傾斜角:±12°(フラット状態に対して)
  - コーナー照明用に設計された対角0.65インチのアレイ
  - 熱抵抗0.5°C/Wの高効率パッケージ
- NIR光（800nm～2000nm）の効率的なステアリング
  - DMD上で最大160Wの入射
  - ウィンドウ伝送効率98%超(950nm～1150nm、2つのウィンドウ表面経由のシングル・パス)
  - ウィンドウ伝送効率93%超(850nm～2000nm、2つのウィンドウ表面経由のシングル・パス)
  - 偏波無依存のアルミニウム製マイクロミラー
- 16ビット、2xLVDS、400MHzの入力データバス
- 専用のDLPC410コントローラ、DLPR410 PROM、DLPA200マイクロミラー・ドライバによる高信頼性で高速の動作
  - 最高12,500Hzのバイナリ・パターン速度
  - グローバル、シングル、デュアル、クワッドのブロック・ミラーのクロッキング・パルス(リセット)動作モード

## 2 アプリケーション

- 3D印刷、選択式レーザー焼結(SLS)
- 動的グレイスケール・レーザー・マーキングおよびコーディング
- 産業用印刷、フレキソ印刷、デジタル製版
- 修理および切除
- 分光器
- 3Dマシン・ビジョンおよび3D生体測定
- 赤外線シーン投影
- ハイパースペクトル画像処理
- 光学スイッチング

## 3 概要

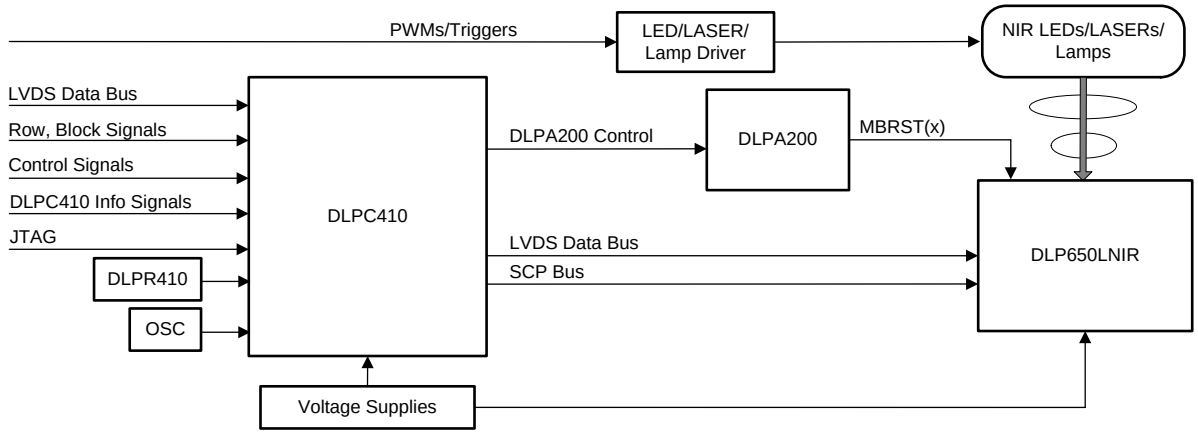
DLP650LNIRデジタル・マイクロミラー・デバイス(DMD)は空間光変調器(SLM)で、近赤外線(NIR)光をステアリングし、高速でパターンを生成して、産業用機器の高度な画像処理に使用できます。熱効率の高いパッケージを使用しているため、DMDを大電力のNIRレーザー照明と組み合わせて、動的なデジタル印刷、焼結、マーキングのソリューションを構築できます。DLP650LNIR、DLPC410、DLPR410、DLPA200チップセットは、1ビットのパターンを最高12,500Hzの速度で生成でき、ピクセル単位で正確なコントロールを行うため、エンジニアは従来のステアリング・レーザーで可能なものより革新的で高精度な光学システムを設計可能です。

**製品情報(1)**

| 型番 | パッケージ | 本体サイズ(公称) |
|---|---|---|
| DLP650LNIR | FYL (149) | 22.30mm×32.20mm |

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。

**アプリケーション概略図**




英語版のTI製品についての情報を翻訳したこの資料は、製品の概要を確認する目的で便宜的に提供しているものです。該当する正式な英語版の最新情報は、www.ti.comで閲覧でき、その内容が常に優先されます。TIでは翻訳の正確性および妥当性につきましては一切保証いたしません。実際の設計などの前には、必ず最新版の英語版をご参照くださいますようお願いいたします。

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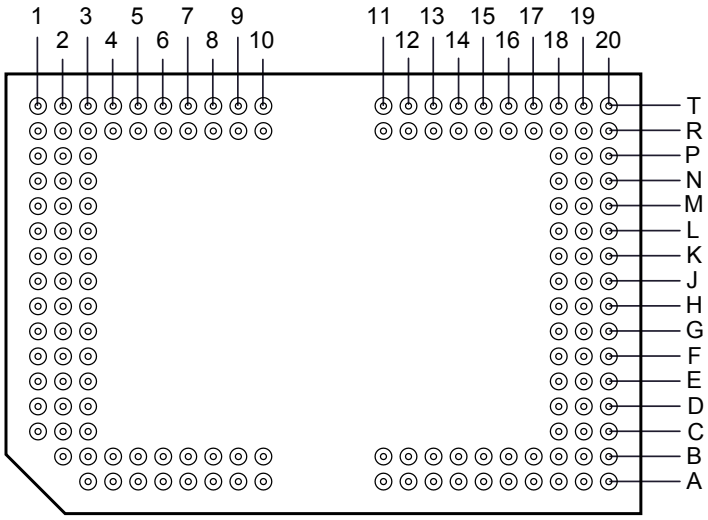
## 4 改訂履歴

| 日付 | リビジョン | 注 |
|---|---|---|
| 2018年11月 | * | 初版 |


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# 5 Pin Configuration and Functions

**FYL Package**
**149-Pin CLGA**
**Bottom View**



**Pin Functions**

| PIN | | NET LENGTH (mils) | SIGNAL | TYPE(1) | DESCRIPTION |
|---|---|---|---|---|---|
| NAME | NO. | | | | |
| **DATA INPUTS** | | | | | |
| D_AN(1) | G20 | 711.64 | LVDS | I | LVDS pair for Data Bus A |
| D_AN(3) | H19 | 711.60 | | | |
| D_AN(5) | F18 | 711.60 | | | |
| D_AN(7) | E18 | 711.60 | | | |
| D_AN(9) | C20 | 711.60 | | | |
| D_AN(11) | B18 | 711.60 | | | |
| D_AN(13) | A20 | 711.60 | | | |
| D_AN(15) | B19 | 711.58 | | | |
| D_AP(1) | H20 | 711.66 | | | |
| D_AP(3) | G19 | 711.61 | | | |
| D_AP(5) | G18 | 711.59 | | | |
| D_AP(7) | D18 | 711.60 | | | |
| D_AP(9) | D20 | 711.59 | | | |
| D_AP(11) | A18 | 711.58 | | | |
| D_AP(13) | B20 | 711.59 | | | |
| D_AP(15) | A19 | 711.59 | | | |
| D_BN(1) | K20 | 711.61 | LVDS | I | LVDS pair for Data Bus B |
| D_BN(3) | J19 | 711.59 | | | |
| D_BN(5) | L18 | 711.59 | | | |
| D_BN(7) | M18 | 711.6 | | | |
| D_BN(9) | P20 | 711.6 | | | |
| D_BN(11) | R18 | 711.59 | | | |
| D_BN(13) | T20 | 711.59 | | | |
| D_BN(15) | R19 | 711.59 | | | |
| D_BP(1) | J20 | 711.61 | | | |
| D_BP(3) | K19 | 711.6 | | | |
| D_BP(5) | K18 | 711.58 | | | |
| D_BP(7) | N18 | 711.58 | | | |
| D_BP(9) | N20 | 711.6 | | | |
| D_BP(11) | T18 | 711.61 | | | |
| D_BP(13) | R20 | 711.59 | | | |
| D_BP(15) | T19 | 711.6 | | | |
| DCLK_AN | D19 | 711.59 | | I | LVDS pair for Data Clock A |
| DCLK_AP | E19 | 711.59 | | | |
| DCLK_BN | N19 | 711.6 | | I | LVDS pair for Data Clock B |
| DCLK_BP | M19 | 711.61 | | | |
| **DATA CONTROL INPUTS** | | | | | |
| SCTRL_AN | F20 | 711.62 | | I | LVDS pair for Serial Control (Sync) A |
| SCTRL_AP | E20 | 711.6 | | | |
| SCTRL_BN | L20 | 711.59 | | I | LVDS pair for Serial Control (Sync) B |
| SCTRL_BP | M20 | 711.59 | | | |

(1) I = Input, O = Output, G = Ground, A = Analog, P = Power, NC = No Connect.


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## Pin Functions (continued)

| PIN | | NET LENGTH (mils) | SIGNAL | TYPE(1) | DESCRIPTION |
|---|---|---|---|---|---|
| NAME | NO. | | | | |
| **MICROMIRROR BIAS RESET INPUTS** | | | | | |
| MBRST(0) | C3 | 507.20 | | I | Non–logic compatible Micromirror Bias Reset signals. Connected directly to the array of pixel micromirrors. Used to hold or release the micromirrors. Bond Pads connect to an internal pull–down resistor. |
| MBRST(1) | D2 | 576.83 | | | |
| MBRST(2) | D3 | 545.78 | | | |
| MBRST(3) | E2 | 636.33 | | | |
| MBRST(4) | G3 | 618.42 | | | |
| MBRST(5) | E1 | 738.25 | | | |
| MBRST(6) | G2 | 718.82 | | | |
| MBRST(7) | G1 | 777.04 | | | |
| MBRST(8) | N3 | 543.29 | | | |
| MBRST(9) | M2 | 612.93 | | | |
| MBRST(10) | M3 | 580.97 | | | |
| MBRST(11) | L2 | 672.43 | | | |
| MBRST(12) | J3 | 653.61 | | | |
| MBRST(13) | L1 | 764.00 | | | |
| MBRST(14) | J2 | 764.37 | | | |
| MBRST(15) | J1 | 813.14 | | | |
| **SCP CONTROL** | | | | | |
| SCPCLK | A8 | | | I | Serial Communications Port Clock. Bond Pad connects to an internal pulldown circuit. |
| SCPDI | A5 | | | I | Serial Communications Port Data. Bond Pad connects to an internal pulldown circuit. |
| SCPENZ | B7 | | | I | Active low serial communications port enable. Bond pad connects to an internal pulldown circuit. |
| SCPDO | A9 | | | O | Serial communications port output. |
| **OTHER SIGNALS** | | | | | |
| EVCC | A3 | | | P | Do Not Connect on the DLP system board. |
| MODE_A | A4 | 415.1 | | I | Data Bus Width Select. Bond Pad connects to an internal pull–down circuit, but for this DMD the PCB also ties this signal to GND. |
| PWRDNZ | B9 | 110.38 | | I | Active Low Device Reset. Bond Pad connects to an internal pull–down circuit. |
| **POWER** | | | | | |
| $V_{CC}$(2) | B11, B12, B13, B16, R12, R13, R16, R17 | | | P | Power supply for low voltage CMOS logic. Power supply for normal high voltage at micromirror address electrodes. |
| $V_{CCI}$(2) | A12, A14, A16, T12, T14, T16 | | | P | Power supply for low voltage CMOS LVDS interface. |
| $V_{CC2}$(2) | C1, D1, M1, N1 | | | P | Power supply for high voltage CMOS logic. Power supply for stepped high voltage at micromirror address electrodes. |

(2) Power supply pins required for all DMD operating modes are $V_{SS}$, $V_{CC}$, $V_{CCI}$, $V_{CC2}$.

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## Pin Functions (continued)

| PIN | | NET LENGTH (mils) | SIGNAL | TYPE(1) | DESCRIPTION |
|---|---|---|---|---|---|
| NAME | NO. | | | | |
| $V_{SS}$ (Ground)(3) | A6, A11, A13, A15, A17, B4, B5, B8, B14, B15, B17, C2, C18, C19, F1, F2, F19, H1, H2, H3, H18, J18, K1, K2, L19, N2, P18, P19, R4, R9, R14, R15, T7, T13, T15, T17 | | | P | Common Return for all power. |
| **RESERVED SIGNALS** | | | | | |
| RESERVED_FC | R7 | 40.64 | | I | Connect to GND on the DLP system board. Bond Pad connects to an internal pull–down circuit. |
| RESERVED_FD | R8 | 94.37 | | I | Connect to GND on the DLP system board. Bond Pad connects to an internal pull–down circuit. |
| RESERVED_PFE | T8 | 50.74 | | I | Connect to ground on the DLP system board. Bond Pad connects to an internal pull-down circuit. |
| RESERVED_STM | B6 | | | I | Connect to GND on the DLP system board. Bond Pad connects to an internal pull–down circuit. |
| RESERVED_TP0 | R10 | 93.3 | | I | Do not connect on the DLP system board. |
| RESERVED_TP1 | T11 | 263.74 | | I | Do not connect on the DLP system board. |
| RESERVED_TP2 | R11 | 281.47 | | I | Do not connect on the DLP system board. |
| RESERVED_BA | T10 | 148.85 | | O | Do not connect on the DLP system board. |
| RESERVED_BB | A10 | 105.28 | | O | Do not connect on the DLP system board. |
| RESERVED_RA1 | T9 | | | O | Do not connect on the DLP system board. |
| RESERVED_RB1 | A7 | | | O | Do not connect on the DLP system board. |
| RESERVED_TS | B10 | 145.42 | | O | Do not connect on the DLP system board. |
| RESERVED_A(0) | T2 | | | NC | Do not connect on the DLP system board. |
| RESERVED_A(1) | T3 | | | | |
| RESERVED_A(2) | R3 | | | | |
| RESERVED_A(3) | T4 | | | | |
| RESERVED_M(0) | R2 | | | NC | Do not connect on the DLP system board. |
| RESERVED_M(1) | P1 | | | NC | Do not connect on the DLP system board. |
| RESERVED_S(0) | T1 | | | NC | Do not connect on the DLP system board. |
| RESERVED_S(1) | R1 | | | NC | Do not connect on the DLP system board. |
| RESERVED_IRQZ | T6 | | | NC | Do not connect on the DLP system board. |
| RESERVED_OEZ | R5 | | | NC | Do not connect on the DLP system board. |
| RESERVED_RSTZ | R6 | | | NC | Do not connect on the DLP system board. |
| RESERVED_STR | T5 | | | NC | Do not connect on the DLP system board. |

(3) $V_{SS}$ must be connected for proper DMD operation.


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**Pin Functions (continued)**

| PIN | | NET LENGTH (mils) | SIGNAL | TYPE(1) | DESCRIPTION |
|---|---|---|---|---|---|
| NAME | NO. | | | | |
| RESERVED_STR | T5 | | | NC | Do not connect on the DLP system board. |
| RESERVED_VB | E3, F3, K3, L3 | | | NC | Do not connect on the DLP system board. |
| RESERVED_VR | B2, B3, P2, P3 | | | NC | Do not connect on the DLP system board. |

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# 6 Specifications

## 6.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted).(1)

| | | MIN | MAX | UNIT |
|---|---|---|---|---|
| **SUPPLY VOLTAGES** | | | | |
| $V_{CC}$ | Supply voltage for LVCMOS core logic(2) | –0.5 | 4 | V |
| $V_{CCI}$ | Supply voltage for LVDS Interface(2) | –0.5 | 4 | V |
| $V_{CC2}$ | Micromirror Electrode and HVCMOS voltage(2)(3) | –0.5 | 9 | V |
| $V_{MBRST}$ | Input voltage for MBRST(15:0)(2) | –28 | 28 | V |
| $\lvert V_{CCI} - V_{CC} \rvert$ | Supply voltage delta (absolute value)(4) | | 0.3 | V |
| **INPUT VOLTAGES** | | | | |
| | Input voltage for all other input pins(2) | –0.5 | $V_{CC}$ + 0.3 | V |
| $\lvert V_{ID} \rvert$ | Input differential voltage (absolute value)(5) | | 700 | mV |
| **ENVIRONMENTAL** | | | | |
| $T_{MIRROR}$ and $T_{WINDOW}$ | Temperature, operating(6) | 0 | 90 | °C |
| | Temperature, non–operating(6) | –40 | 90 | °C |
| $\lvert T_{DELTA} \rvert$ | Absolute Temperature delta between any point on the window edge and the ceramic test point TP1(7) | | 30 | °C |
| $T_{DP}$ | Dew point temperature, operating and non–operating (noncondensing) | | 81 | °C |

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are referenced to common ground $V_{SS}$. $V_{CC}$, $V_{CCI}$, $V_{CC2}$ power supplies are all required for all DMD operating modes. $V_{MBRST}$signals are also required to be at the appropriate voltage at the appropriate time as controlled by the DLPC410 and DLPA200.
(3) $V_{CC2}$ supply transients must fall within specified voltages.
(4) Exceeding the recommended allowable voltage difference between $V_{CC}$ and $V_{CCI}$ may result in excessive current draw.
(5) The maximum LVDS input voltage rating applies when each input of a differential pair is at the same voltage potential.
(6) The highest micromirror temperature (as calculated using *Micromirror Temperature Calculations*) or of any point along the window edge as defined in Figure 20. The locations of thermal test points TP2, TP3, TP4, and TP5 in Figure 20 are intended to measure the highest window edge temperature. If a particular application causes another point on the window edge to be at a higher temperature, use that point.
(7) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in Figure 20. The window test points TP2, TP3, TP4, and TP5 shown in Figure 20 are intended to result in the worst case delta. If a particular application causes another point on the window edge to result in a larger delta temperature, then use that point.


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## 6.2 Storage Conditions

Applicable for the DMD as a component or non-operating in a system.

| | | MIN | MAX | UNIT |
|---|---|---|---|---|
| $T_{DMD}$ | DMD storage temperature | –40 | 80 | °C |
| $T_{DP-AVG}$ | Average dew point temperature (non-condensing) (1) | | 28 | °C |
| $T_{DP-ELR}$ | Elevated dew point temperature range (non-condensing) (2) | 28 | 36 | °C |
| $CT_{ELR}$ | Cumulative time in elevated dew point temperature range | | 24 | Months |

(1) The average over time (including storage and operating) that the device is not in the elevated dew point temperature range.
(2) Limit exposure to dew point temperatures in the elevated range during storage and operation to less than a total cumulative time of $CT_{ELR}$.

## 6.3 ESD Ratings

| | | | | VALUE | UNIT |
|---|---|---|---|---|---|
| $V_{(ESD)}$ | Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1) | All pins except MBRST(15:0) | ±2000 | V |
| | | | Pins MBRST(15:0) | < 250 | |

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

## 6.4 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted). The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by this table. No level of performance is implied when operating the device above or below these limits.

| | | MIN | NOM | MAX | UNIT |
|---|---|---|---|---|---|
| **VOLTAGE SUPPLY** | | | | | |
| $V_{CC}$ | Supply voltage for LVCMOS core logic (1) | 3.0 | 3.3 | 3.6 | V |
| $V_{CCI}$ | Supply voltage for LVDS Interface (1) | 3.0 | 3.3 | 3.6 | V |
| $V_{CC2}$ | Micromirror Electrode and HVCMOS voltage (1) (2) | 8.25 | 8.5 | 8.75 | V |
| $V_{MBRST}$ | Micromirror Bias / Reset Voltage (1) | –27 | | 26.5 | V |
| $\lvert V_{CC} - V_{CCI} \rvert$ | Supply voltage delta (absolute value) (3) | | 0 | 0.3 | V |
| **LVCMOS INTERFACE** | | | | | |
| $V_{IH}$ | Input High Voltage | 1.7 | 2.5 | $V_{CC}$ + 0.3 | V |
| $V_{IL}$ | Input Low Voltage | –0.3 | | 0.7 | V |
| $I_{OH}$ | High Level Output Current | | | –20 | mA |
| $I_{OL}$ | Low Level Output Current | | | 15 | mA |
| $t_{PWRDNZ}$ | PWRDNZ pulse width (4) | 10 | | | ns |
| **SCP INTERFACE** | | | | | |
| $f_{SCPCLK}$ | SCP clock frequency (5) | 50 | | 500 | kHz |
| $t_{SCP_PD}$ | Propagation delay, clock to Q, from rising-edge of SCPCLK to valid SCPDO. (6) | 0 | | 900 | ns |
| $t_{SCP_DS}$ | SCPDI clock setup time (before SCPCLK falling-edge) (6) | 800 | | | ns |
| $t_{SCP_DH}$ | SCPDI hold time (after SCPCLK falling-edge) (6) | 900 | | | ns |
| $t_{SCP_NEG_ENZ}$ | Time between falling–edge of SCPENZ and the rising–edge of SCPCLK. (5) | 1 | | | us |
| $_{SCP_POS_ENZ}$ | Time between falling-edge of SCPCLK and the rising–edge of SCPENZ | 1 | | | us |
| $t_{SCP_OUT_EN}$ | Time required for SCP output buffer to recover after SCPENZ (from tri-state). | | | 192/$f_{DCLK}$ | s |

(1) All voltages are referenced to $V_{SS}$ (common ground). $V_{CC}$, $V_{CCI}$, $V_{CC2}$, and $V_{MBRST}$ power supplies are all required for proper DMD operation. $V_{SS}$ must also be connected to common ground.
(2) $V_{CC2}$ supply transients must fall within specified max voltages.
(3) To prevent excess current, the supply voltage delta $\lvert V_{CCI} - V_{CC} \rvert$ must be less than the specified limit.
(4) PWRDNZ input pin resets the SCP and disables the LVDS receivers. PWRDNZ input pin overrides SCPENZ input pin and tri-states the SCPDO output pin.
(5) The SCP clock is a gated clock. Duty cycle must be 50% ± 10%. SCP parameter is related to the frequency of DCLK.
(6) See Figure 3.

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## Recommended Operating Conditions (continued)

Over operating free-air temperature range (unless otherwise noted). The functional performance of the device specified in this data sheet is achieved when operating the device within the limits defined by this table. No level of performance is implied when operating the device above or below these limits.

| | | MIN | NOM | MAX | UNIT |
|---|---|---|---|---|---|
| $t_{SCP_PW_ENZ}$ | SCPENZ inactive pulse width (high level) | 1 | | | $1/f_{scpclk}$ |
| $t_r$ | Rise Time (20% to 80%). See (6) | | | 200 | ns |
| $t_f$ | Fall time (80% to 20%). See (6) | | | 200 | ns |
| **LVDS INTERFACE** | | | | | |
| $f_{CLOCK}$ | Clock frequency for LVDS interface (all channels), DCLK (7) | 395 | 400 | 405 | MHz |
| $\|V_{ID}\|$ | Input differential voltage (absolute value) (8) | 100 | 400 | 600 | mV |
| $V_{CM}$ | Common mode voltage (8) | | 1200 | | mV |
| $V_{LVDS}$ | LVDS voltage (8) | 0 | | 2000 | mV |
| $t_{LVDS_RSTZ}$ | Time required for LVDS receivers to recover from PWRDNZ | | | 10 | ns |
| $Z_{IN}$ | Internal differential termination resistance | 95 | | 105 | Ω |
| $Z_{LINE}$ | Line differential impedance (PWB/trace) | 90 | 100 | 110 | Ω |
| **ENVIRONMENTAL** | | | | | |
| $T_{MIRROR}$ | Micromirror temperature, long–term operational (9) (10) (11) | 10 | | 40 to 70 (12) | °C |
| | Micromirror temperature, short–term operational (10) (13) | 0 | | 10 | °C |
| $T_{WINDOW}$ | Window temperature–operational (14) | 10 | | 85 | °C |
| $T_{\|DELTA\|}$ | Absolute temperature delta between any point on the window edge and the ceramic test point TP1. (15) | | | 26 | °C |
| $T_{DP\ -AVG}$ | Average dew point temperature (non–condensing) (16) | | | 28 | °C |
| $T_{DP-ELR}$ | Elevated dew point temperature range (non-condensing) (17) | 28 | | 36 | °C |
| $CT_{ELR}$ | Cumulative time in elevated dew point temperature range | | | 24 | Months |
| $ILL_{UV}$ | Illumination Power Density < 420 nm (9) | | | 10 | $mW/cm^2$ |
| $ILL_{VIS-NIR}$ | Illumination Power Density between 420 nm and 950 nm | | | 40 | $W/cm^2$ |
| $ILL_{NIR2A}$ | Illumination Total Power between 950 nm and 1150 nm (18) | | | 160 | W |
| $ILL_{NIR2B}$ | Illumination Power Density between 950 nm and 1150 nm (18) | | | 500 | $W/cm^2$ |
| $ILL_{NIR3}$ | Illumination Power Density between 1150 nm and 2000 nm | | | 40 | $W/cm^2$ |
| $ILL_{IR}$ | Illumination Power Density > 2000 nm | | | 10 | $mW/cm^2$ |

(7) See LVDS Timing Requirements in *Timing Requirements* and Figure 7.
(8) See Figure 6 LVDS Waveform Requirements.
(9) Simultaneous exposure of the DMD to the maximum *Recommended Operating Conditions* for temperature and UV illumination reduces device lifetime.
(10) The mirror temperatures cannot be measured directly and must be computed analytically from the temperature measured at test point 1 (TP1) shown in Figure 20 and the DMD package and mirror *thermal resistances* using the *Micromirror Temperature Calculations*.
(11) Long-term is defined as the usable life of the device.
(12) Per Figure 2, derate the maximum operational micromirror temperature based on the micromirror landed duty cycle that the DMD experiences in the end application. See *Micromirror Landed-On/Landed-Off Duty Cycle* for a definition of micromirror landed duty cycle.
(13) Mirror temperatures beyond those specified as long-term are recommended for short-term conditions only (power-up). Short-term is defined as cumulative time over the usable life of the device and is less than 500 hours.
(14) The locations of thermal test points TP2, TP3, TP4, and TP5 in Figure 20 are intended to measure the highest window edge temperature. For most applications, the locations shown are representative of the highest window edge temperature. If a particular application causes additional points on the window edge to be at a higher temperature, add test points to those locations.
(15) Temperature delta is the highest difference between the ceramic test point 1 (TP1) and anywhere on the window edge as shown in Figure 20. The window test points TP2, TP3, TP4, and TP5 shown in Figure 20 are intended to result in the worst case delta temperature. If a particular application causes another point on the window edge to result in a larger delta temperature, use that point.
(16) The average over time (including storage and operating) that the device is not in the 'elevated dew point temperature range'.
(17) Limit exposure to dew point temperatures in the elevated range during storage and operation to less than a total cumulative time of $CT_{ELR}$.
(18) See Figure 1 for allowable combinations of illumination power vs illumination power density. 160W total power is achievable only by full array illumination. 500 $W/cm^2$ is only achievable through partial array illumination. Some combinations of illumination power and power density require cooling of the window with forced air as defined by Figure 1. Refer to the application note DLP® High Power Thermal Design Guide: Focus on High Power NIR Laser Illumination for additional details.


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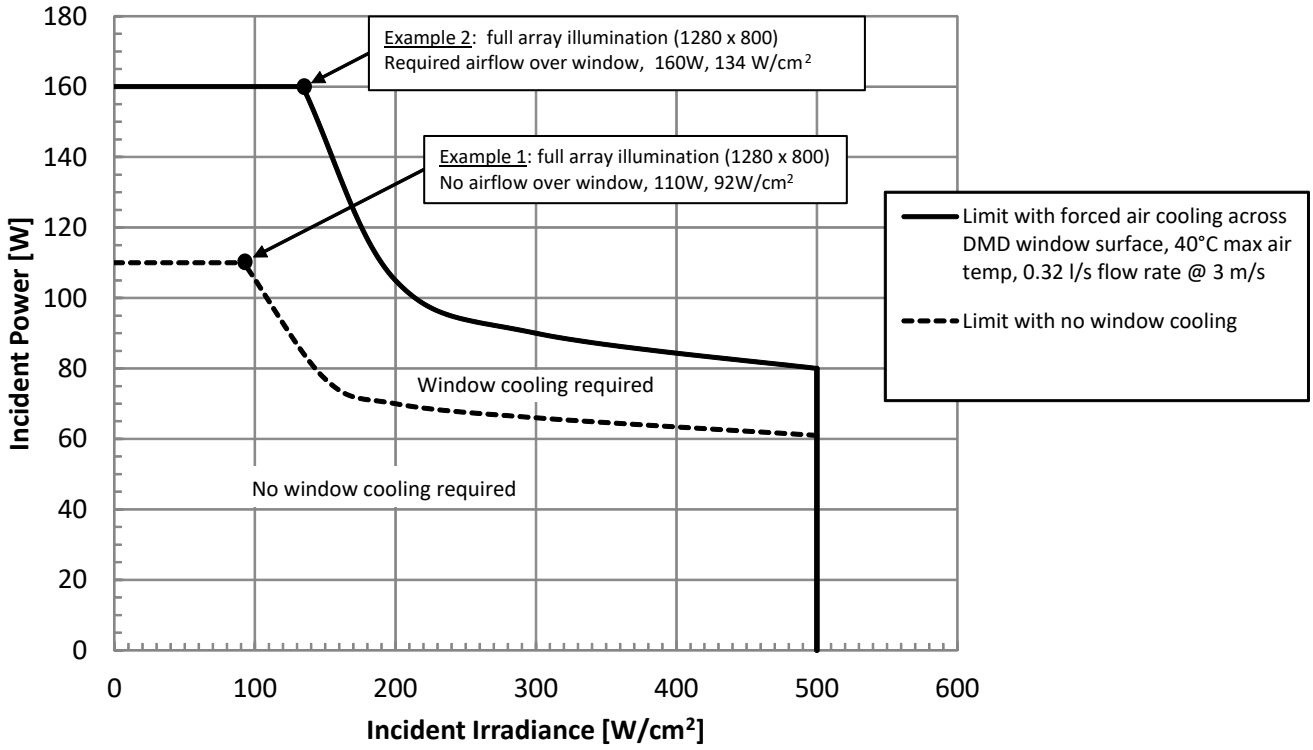



**Figure 1. Maximum Recommended Illumination Incident Power vs Incident Irradiance**

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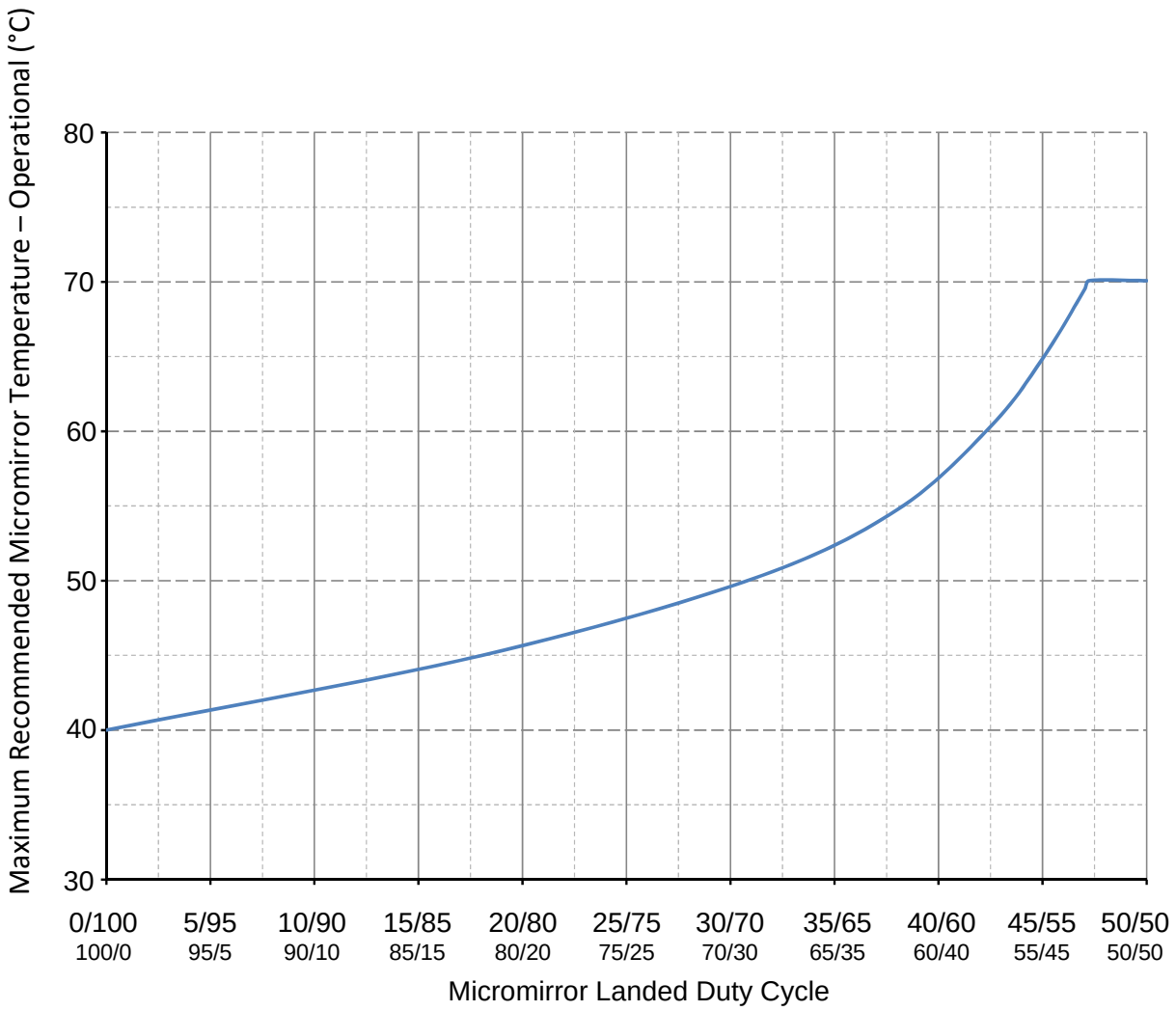



**Figure 2. Maximum Recommended Micromirror Temperature - Derating Curve (see Landed Duty Cycle and Operational DMD Temperature)**

## 6.5 Thermal Information

| THERMAL METRIC | DLP650LNIR FYL Package 149 PINS | UNIT |
|---|---|---|
| $R_{SILICON\text{-}TO\text{-}CERAMIC}$: Thermal resistance, silicon to ceramic, as measured at test point 1 (TP1) (1) | 0.5 | °C/W |
| $R_{MIRROR\text{-}TO\text{-}SILICON}$: Thermal resistance, mirror to silicon, per individual mirror (1) | $3.39 \times 10^5$ | °C/W |

(1) The DMD is designed to conduct absorbed and dissipated heat to the back of the package. The cooling system must be capable of maintaining the package within the temperature range specified in the *Recommended Operating Conditions*.
The total heat load on the DMD is largely driven by the incident light absorbed by the micromirrror array, although other contributions include light energy outside of the active mirror array and electrical power dissipation of the silicon.
Design the optical system to minimized light outside of the active micromirror array because light outside of this area gets highly absorbed by the optical border and increases DMD heat load.
Design the optical system to minimize the light energy falling outside the window clear aperture. Aditional thermal load in this area contributes to window heating and significantly degrades the reliability of the device.


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## 6.6 Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted).

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{OH}$ | High level output voltage | $V_{CC}$ = 3 V, $I_{OH}$ = – 20 mA | 2.4 | | | V |
| $V_{OL}$ | Low level output voltage | $V_{CC}$ = 3.6 V, $I_{OL}$ = 15 mA | | | 0.4 | V |
| $I_{OZ}$ | High impedance output current | $V_{CC}$ = 3.6 V | | | 10 | µA |
| $I_{IL}$ | Low level input current | $V_{CC}$ = 3.6 V, VI = 0 | | | –60 | µA |
| $I_{IH}$ | High level input current (1) | $V_{CC}$ = 3.6 V, VI = $V_{CC}$ | | | 200 | µA |
| $I_{CC}$ | Supply current VCC (2) | $V_{CC}$ = 3.6 V | | | 650 | mA |
| $I_{CCI}$ | Supply current VCCI (2) | $V_{CCI}$ = 3.6 V | | | 350 | mA |
| $I_{CC2}$ | Supply current VCC2 | $V_{CC2}$ = 8.75 V | | | 25 | mA |
| $Z_{IN}$ | Internal differential termination resistance | | 95 | | 105 | Ω |
| $Z_{LINE}$ | Line differential impedance (PWB/trace) | | 90 | 100 | 110 | Ω |
| $C_I$ | Input capacitance (1) | f = 1 MHz | | | 10 | pF |
| $C_O$ | Output capacitance (1) | f = 1 MHz | | | 10 | pF |
| $C_{IM}$ | Input capacitance for MBRST[0:15] pins | f = 1 MHz | 160 | | 210 | pF |

(1) Applies to LVCMOS pins only. Excludes LVDS pins and test pad pins.
(2) To prevent excess current, the supply voltage delta $|V_{CCI} – V_{CC}|$ must be less than the specified limit in *Recommended Operating Conditions*.

## 6.7 Timing Requirements

Over *Recommended Operating Conditions* (unless otherwise noted).

| PARAMETER DESCRIPTION | | SIGNAL | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| **LVDS** (1) | | | | | | |
| $t_C$ | Clock Cycle Duration for DCLK_A | LVDS | 2.46 | | | ns |
| $t_C$ | Clock Cycle Duration for DCLK_B | LVDS | 2.46 | | | ns |
| $t_W$ | Pulse Duration for DCLK_A | LVDS | 1.07 | 1.23 | | ns |
| $t_W$ | Pulse Duration for DCLK_B | LVDS | 1.07 | 1.23 | | ns |
| $t_{SU}$ | Setup Time for D_A(15:0) before DCLK_A | LVDS | 0.35 | | | ns |
| $t_{SU}$ | Setup Time for D_A(15:0) before DCLK_B | LVDS | 0.35 | | | ns |
| $t_{SU}$ | Setup Time for SCTRL_A before DCLK_A | LVDS | 0.35 | | | ns |
| $t_{SU}$ | Setup Time for SCTRL_B before DCLK_B | LVDS | 0.35 | | | ns |
| $t_H$ | Hold time for D_A(15:0) after DCLK_A | LVDS | 0.50 | | | ns |
| $t_H$ | Hold time for D_B(15:0) after DCLK_B | LVDS | 0.50 | | | ns |
| $t_H$ | Hold Time for SCTRL_A after DCLK_A | LVDS | 0.50 | | | ns |
| $t_H$ | Hold Time for SCTRL_B after DCLK_B | LVDS | 0.50 | | | ns |
| $t_{SKEW}$ | Channel B relative to Channel A (2) (3) | LVDS | –1.23 | | 1.23 | ns |

(1) See Figure 7 for timing requirements for LVDS.
(2) Channel A (Bus A) includes the following LVDS pairs: DCLK_AN and DCLK_AP, SCTRL_AN and SCTRL_AP, D_AN(15,13,11,9,7,5,3,1) and D_AP(15,13,11,9,7,5,3,1).
(3) Channel B (Bus B) includes the following LVDS pairs: DCLK_BN and DCLK_BP, SCTRL_BN and SCTRL_BP, D_BN(15,13,11,9,7,5,3,1) and D_BP(15,13,11,9,7,5,3,1).

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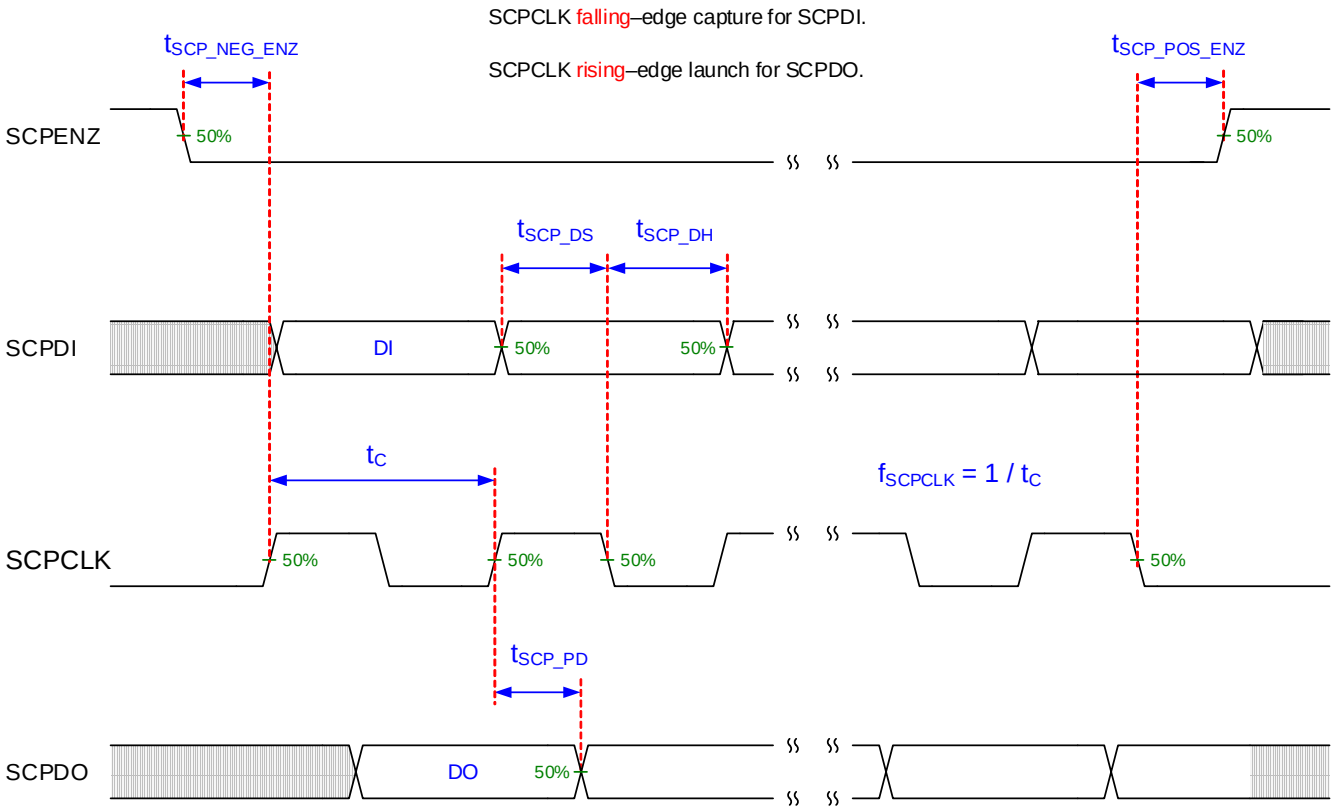
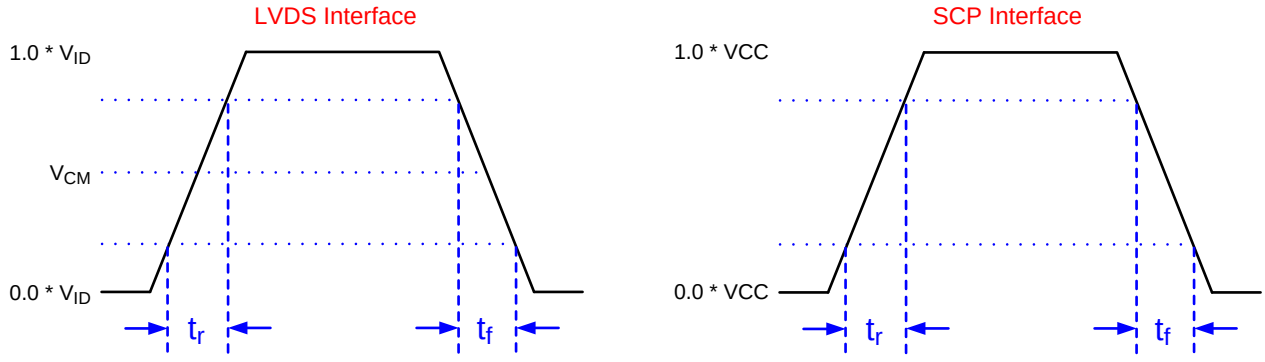



**Figure 3. SCP Timing Requirements**

See *Recommended Operating Conditions* for $f_{SCPCLK}$, $t_{SCP_DS}$, $t_{SCP_DH}$, and $t_{SCP_PD}$ specifications.

See *Recommended Operating Conditions* for $t_r$ and $t_f$ specifications and conditions.




Not to scale.

Refer to the *Timing Requirements*.

Refer to for list of LVDS pins and SCP pins.

**Figure 4. Rise Time and Fall Time**


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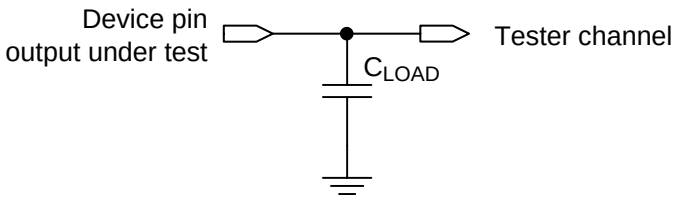



**Figure 5. Test Load Circuit for Output Propagation Measurement**

For output timing analysis, the tester pin electronics and its transmission line effects must be taken into account. Use IBIS or other simulation tools to correlate the timing reference load to a system environment. See Figure 5.

Not to Scale

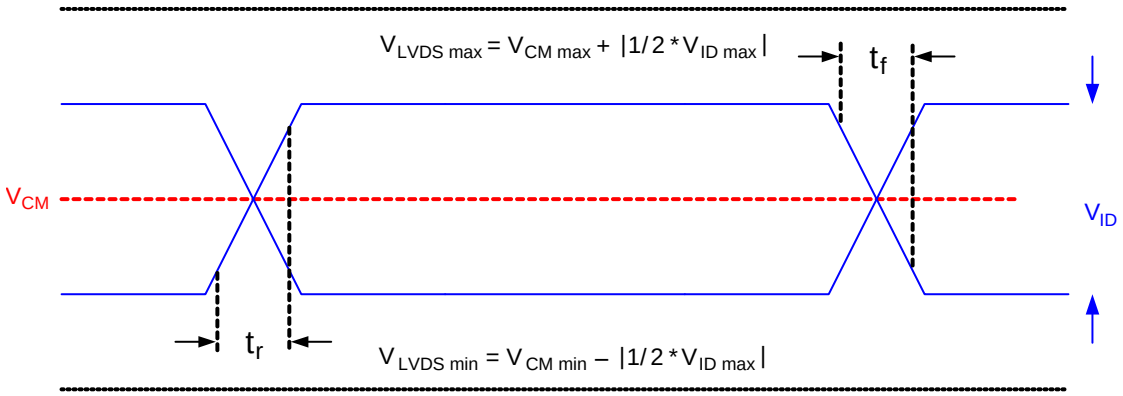



**Figure 6. LVDS Waveform Requirements**

See *Recommended Operating Conditions* for $V_{CM}$, $V_{ID}$, and $V_{LVDS}$ specifications and conditions.

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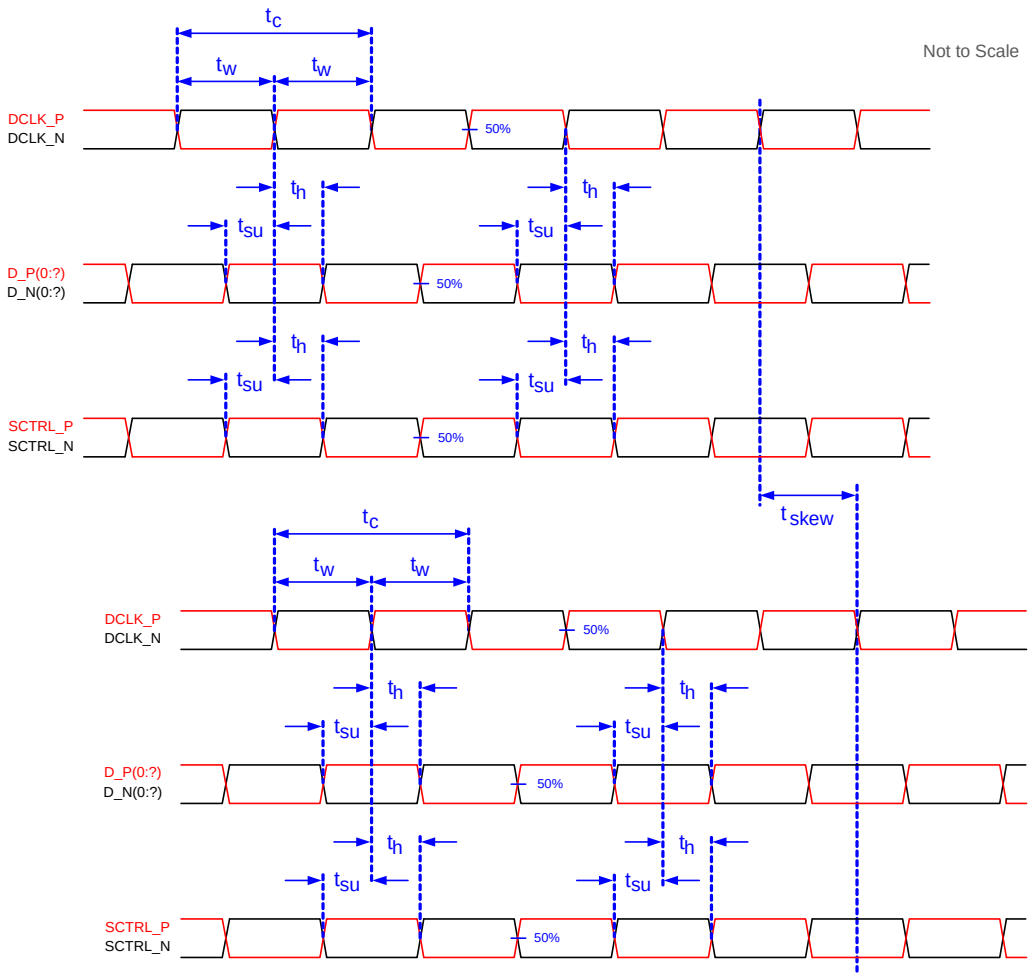



**Figure 7. Timing Requirements**

See *Timing Requirements* for timing requirements and LVDS pairs per channel (bus) defining D_P(0:x) and D_N(0:x).

## 6.8 System Mounting Interface Loads

**Table 1. System Mounting Interface Loads**

| PARAMETER | MIN | NOM | MAX | UNIT |
|---|---|---|---|---|
| Condition 1: | | | | |
| • Thermal Interface area(1) | | | 11.3 | kg |
| • Electrical Interface area(1) | | | 11.3 | kg |
| Condition 2: | | | | |
| • Thermal Interface area(1) | | | 0 | kg |
| • Electrical Interface area(1) | | | 22.6 | kg |

(1) Uniformly distributed within area shown in Figure 8.


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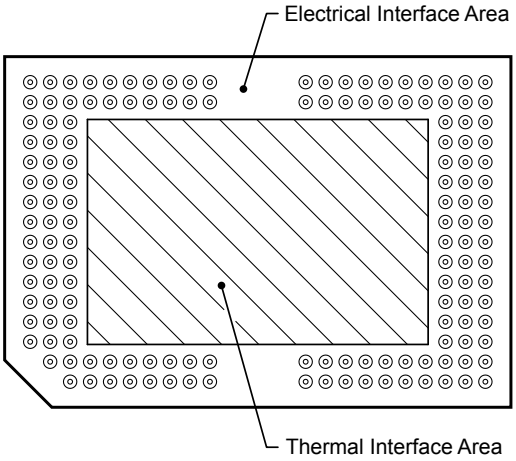



**Figure 8. System Mounting Interface Loads**

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## 6.9 Micromirror Array Physical Characteristics

**Table 2. Micromirror Array Physical Characteristics**

| PARAMETER DESCRIPTION | | VALUE | UNIT |
|---|---|---|---|
| Number of active columns (1) | M | 1280 | micromirrors |
| Number of active rows (1) | N | 800 | |
| Micromirror (pixel) pitch (1) | P | 10.8 | µm |
| Micromirror active array width (1) | Micromirror pitch × number of active columns | 13.824 | mm |
| Micromirror active array height (1) | Micromirror pitch × number of active rows | 8.640 | mm |
| Micromirror active border size (2) | Pond of Micromirror (POM) | 10 | micromirrors / side |

(1) See Figure 9.
(2) The structure and qualities of the border around the active array includes a band of partially functional micromirrors called the *Pond Of Mirrors* (POM). These micromirrors are structurally and/or electrically prevented from tilting toward the bright or "on" state but the requirement of an electrical bias to tilt toward "off remains."

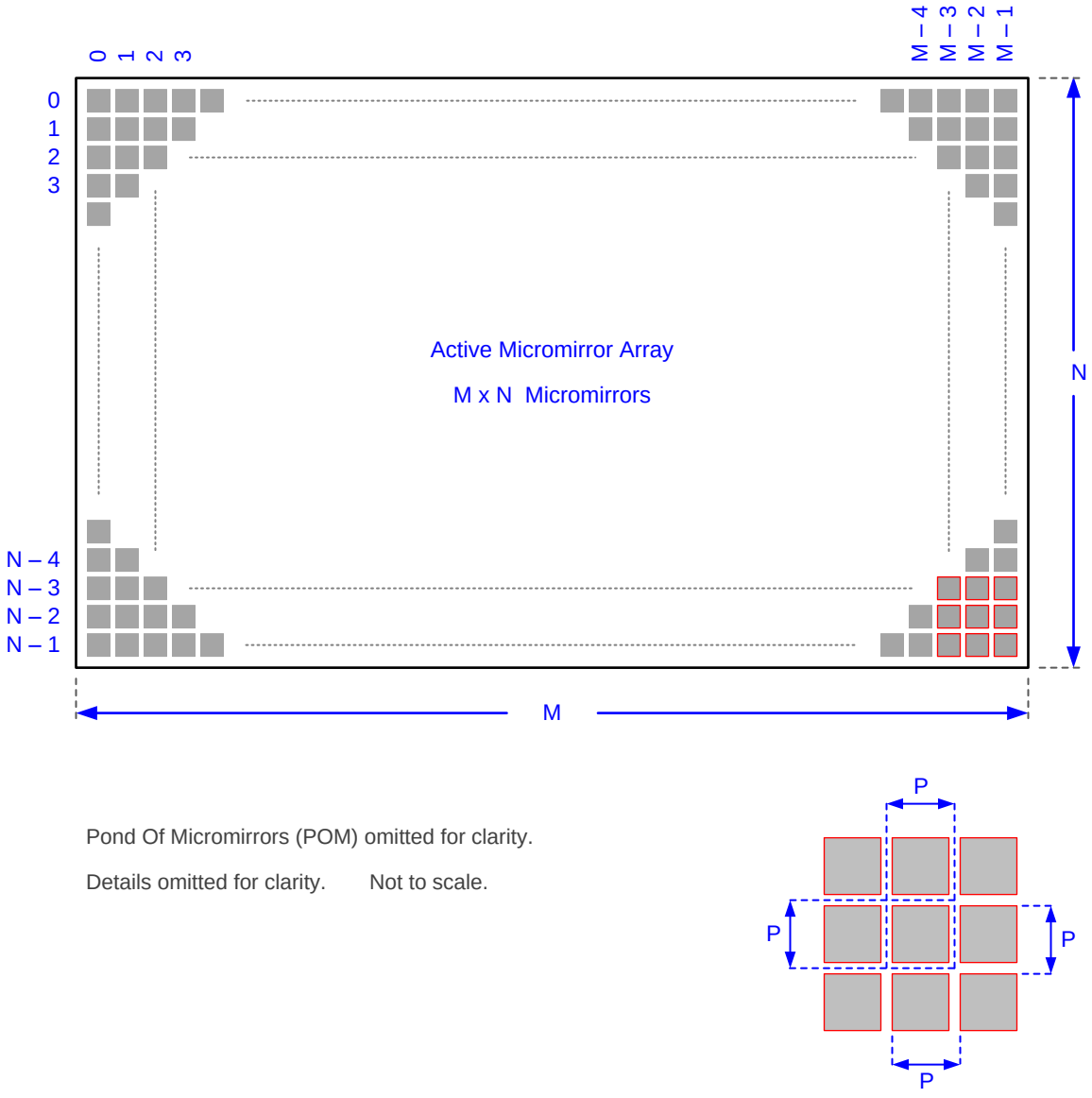



**Figure 9. Micromirror Array Physical Characteristics**

Refer to the *Micromirror Array Physical Characteristics* table for M, N, and P specifications.


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## 6.10 Micromirror Array Optical Characteristics

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-offs between numerous component and system design parameters. See the additional details, considerations, and guidelines: DLP System Optics Application Report (listed in DLPS022) for guidelines.

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| a | Micromirror tilt angle | DMD parked state (1) (2), See Figure 15 | | 0 | | degrees |
| | | DMD landed state (1) (3) (4) See Figure 15 | | 12 | | |
| β | Micromirror tilt angle variation (1) (3) (5) (6) (7) | See Figure 15 | –1 | | 1 | degrees |
| | Micromirror crossover time (8) | | | 3 | | µs |
| | Micromirror switching time (9) | | | 13 | 22 | µs |
| | Array switching time at 400 MHz with global reset (10) | | 92.5 | | | µs |
| | Non-operating micromirrors (11) | Non-adjacent micromirrors | | | 10 | micromirrors |
| | | Adjacent micromirrors | | | 0 | |
| | Orientation of the micromirror axis-of-rotation (12) | See Figure 15 | 44 | 45 | 46 | degrees |
| | Micromirror array optical efficiency (13) (14) | @1064 nm, with all micromirrors in the ON state | | 75% | | |

(1) Measured relative to the plane formed by the overall micromirror array.
(2) Parking the micromirror array returns all of the micromirrors to an essentially flat (0˚) state (as measured relative to the plane formed by the overall micromirror array).
(3) Additional variation exists between the micromirror array and the package datums- see the *メカニカル、パッケージ、および注文情報*
(4) When the micromirror array is landed, the tilt angle of each individual micromirror is dictated by the binary contents of the CMOS memory cell associated with each individual micromirror. A binary value of 1 results in a micromirror landing in an nominal angular position of +12°. A binary value of 0 results in a micromirror landing in an nominal angular position of –12°.
(5) Represents the landed tilt angle variation relative to the nominal landed tilt angle.
(6) Represents the variation that can occur between any two individual micromirrors, located on the same device or located on different devices.
(7) For some applications, it is critical to account for the micromirror tilt angle variation in the overall system optical design. With some system optical designs, the micromirror tilt angle variation within a device may result in perceivable non-uniformities in the light field reflected from the micromirror array. With some system optical designs, the micromirror tilt angle variation between devices may result in colorimetry variations and/or system contrast variation.
(8) Micromirror crossover time is the transition time from landed to landed during a crossover transition and primarily a function of the natural response time of the micromirrors.
(9) Micromirror switching time is the time after a micromirror clocking pulse until the micromirrors can be addressed again. It includes the micromirror settling time.
(10) Array switching is controlled and coordinated by the DLPC410 (DLPS024) and DLPA200 (DLPS015). Nominal switching time depends on the system implementation and represents the time for the entire micromirror array to be refreshed (array loaded plus reset and mirror settling time).
(11) Non-operating micromirror is defined as a micromirror that is unable to transition nominally from the –12° position to +12° or vice versa.
(12) Measured relative to the package datums 'B' and 'C', shown in the *メカニカル、パッケージ、および注文情報*.
(13) The minimum or maximum DMD optical efficiency observed in a specific application depends on numerous application-specific design variables, such as:
  (a) Illumination wavelength, bandwidth/line-width, degree of coherence
  (b) Illumination angle, plus angle tolerance
  (c) Illumination and projection aperture size, and location in the system optical path
  (d) Illumination overfill of the DMD micromirror array
  (e) Aberrations present in the illumination source and/or path
  (f) Aberrations present in the projection path

  The specified nominal DMD optical efficiency is based on the following use conditions:
  (a) NIR illumination (1064nm selected as reference example)
  (b) Input illumination optical axis oriented at 24° relative to the window normal
  (c) Projection optical axis oriented at 0° relative to the window normal
  (d) *ƒ* / 3 illumination aperture
  (e) *ƒ* / 2.4 projection aperture

  Based on these use conditions, the nominal DMD optical efficiency at 1064 nm results from the following four components:
  (a) Micromirror array fill factor: nominally 94%
  (b) Micromirror array diffraction efficiency: nominally 88%
  (c) Micromirror surface reflectivity: nominally 94%
  (d) Window transmission: nominally 98% (single pass, through two surface transitions)
(14) Does not account for the effect of micromirror switching duty cycle, which is application dependent. Micromirror switching duty cycle represents the percentage of time that the micromirror is actually reflecting light from the optical illumination path to the optical projection path. This duty cycle depends on the illumination aperture size, the projection aperture size, and the micromirror array update rate.

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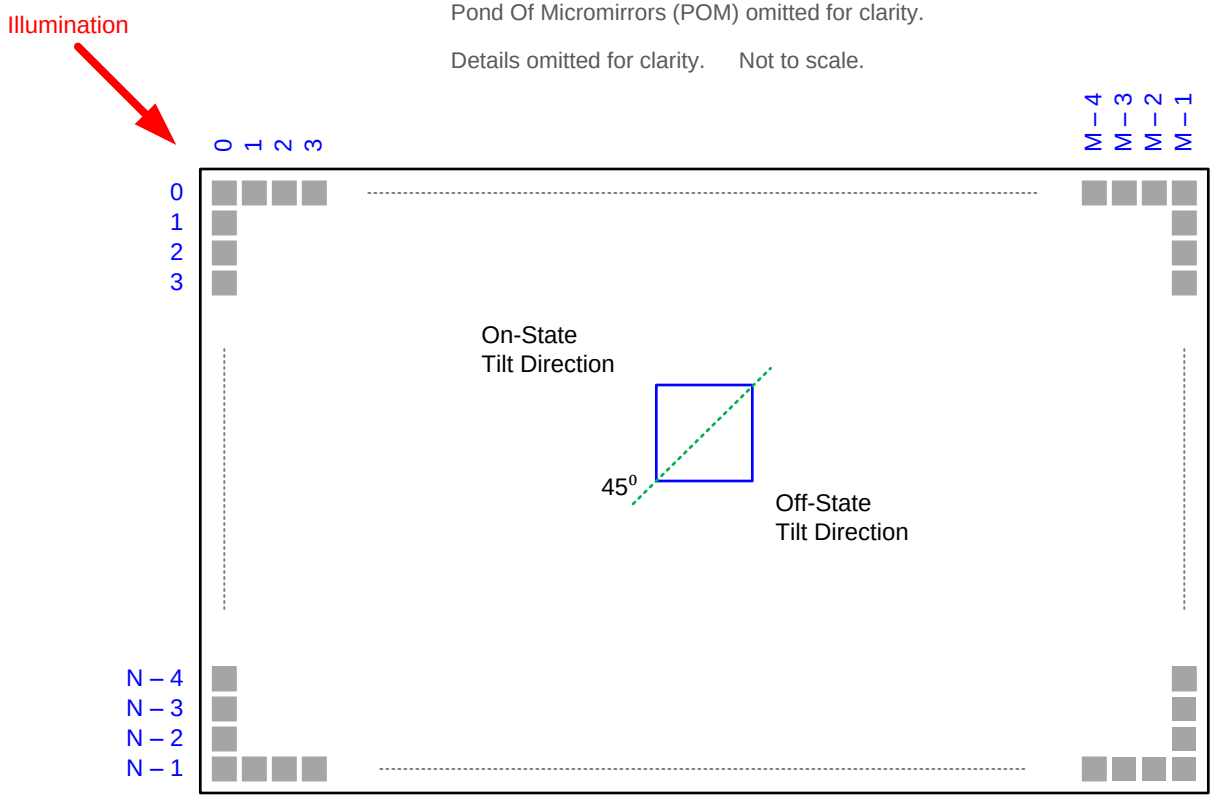



**Figure 10. Micromirror Landed Orientation and Tilt**

Refer to the *Micromirror Array Physical Characteristics* table for M, N, and P specifications.

## 6.11 Window Characteristics

| PARAMETER (1) | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| Window material designation | Corning Eagle XG | | | | |
| Window refractive index | At wavelength 1060 nm | | 1.4996 | | |
| Window aperture | See (2) | | | | |
| Illumination overfill | Refer to *Illumination Overfill* | | | | |
| Window transmittance, single–pass through both surfaces and glass (3) | At wavelength 1050 nm. Applies to 0° AOI only. | | 99% | | |
| | Minimum within the wavelength range 850 nm to 2000 nm. Applies to 0° AOI only. | 90% | 93% | | |
| | Minimum within the wavelength range 950 nm to 1150 nm. Applies to 0° AOI only. | 98% | 98.4% | | |

(1) See *Optical Interface and System Image Quality Considerations* for more information.
(2) For details regarding the size and location of the window aperture, see the package mechanical characteristics listed in the Mechanical ICD in the Mechanical, Packaging, and Orderable Information section.
(3) See the TI application report DLPA031, *Wavelength Transmittance Considerations for DLP DMD Window*.

## 6.12 Chipset Component Usage Specification

Reliable function and operation of the DLP650LNIR DMD requires that it be used in conjunction with the other components of the applicable DLP chipset, including those components that contain or implement TI DMD control technology. TI DMD control technology consists of the TI technology and devices used for operating or controlling a DLP DMD.


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# 7 Detailed Description

## 7.1 Overview

Optically, the DLP650LNIR consists of 1,024,000 highly reflective, digitally switchable, micrometer-sized mirrors (micromirrors), organized in a two-dimensional array of 1280 micromirror columns by 800 micromirror rows. Each aluminum micromirror is approximately 10.8 microns in size (see the *Micromirror Pitch* in ) and is switchable between two discrete angular positions: –12° and 12°. The angular positions are measured relative to a 0° flat state, which is parallel to the array plane (see Figure 15). The tilt direction is perpendicular to the hinge-axis, which is positioned diagonally relative to the overall array. The On State landed position is directed toward row 0, column 0 (upper left) corner of the device package (see the *Micromirror Hinge-Axis Orientation* in ). In the field of visual displays, the 1280 × 800 pixel resolution is referred to as WXGA or WXGA-800.

Each individual micromirror is positioned over a corresponding CMOS memory cell. The angular position of a specific micromirror is determined by the binary state (logic 0 or 1) of the corresponding CMOS memory cell contents, after the mirror clocking pulse is applied. The angular position (–12° or +12°) of the individual micromirrors changes synchronously with a micromirror clocking pulse, rather than being synchronous with the CMOS memory cell data update. Therefore, writing a logic 1 into a memory cell followed by a mirror clocking pulse results in the corresponding micromirror switching to a 12° position. Writing a logic 0 into a memory cell followed by a mirror clocking pulse results in the corresponding micromirror switching to a –12° position.

Updating the angular position of the micromirror array consists of two steps. First, updating the contents of the CMOS memory. Second, application of a micromirror clocking pulse to all or a portion of the micromirror array (depending upon the configuration of the system). Micromirror clocking pulses are generated externally by the DLPA200 device, with application of the pulses being coordinated by the DLPC410 controller.

Around the perimeter of the 1280 by 800 array of micromirrors is a uniform band of border micromirrors. The border micromirrors are not user-addressable. The border micromirrors land in the –12° position once power has been applied to the device. There are 10 border micromirrors on each side of the 1280 by 800 active array.

Figure 11 shows a DLPC410 and DLP650LNIR chipset block diagram. The DLPC410 and DLPA200 control and coordinate the data loading and micromirror switching for reliable DLP650LNIR operation. The DLPR410 is the programmed PROM required to properly configure the DLPC410 controller. For more information on the chipset components, see *Feature Description*. For a typical system application using the DLPC410 and chipset components including a DLP650LNIR DMD, see Figure 21.

## 7.2 System Functional Block Diagram

Figure 11 shows a simplified system block diagram with the use of the DLPC410 with the following chipset components:

**DLPC410** Xilinx [XC5VLX30] FPGA configured to provide high-speed DMD data and control, and DLPA200 timing and control

**DLPR410** [XCF16PFSG48C] serial flash PROM contains startup configuration information (EEPROM)

**DLPA200** DMD micromirror driver for the DLP650LNIR DMD

**DLP650LNIR** Spatial light modulator (DMD)

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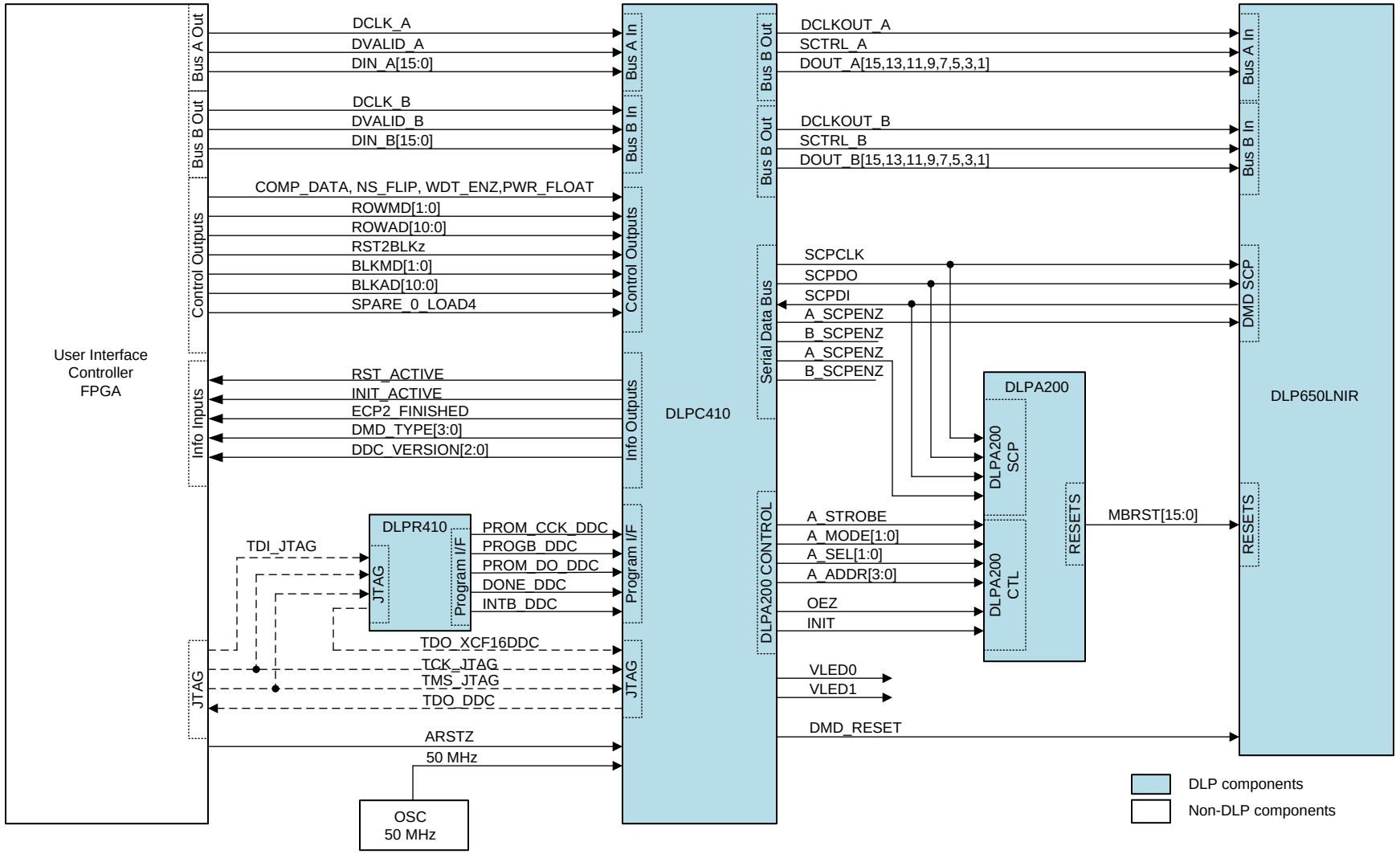



**Figure 11. DLPC410, DLPA200, DLPR410, and DLP650LNIR Functional Block Diagram**


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## 7.3 Feature Description

**Table 3. DMD Overview**

| DMD | ARRAY | QUAD BLOCK MODE (Patterns/s) | GLOBAL RESET MODE (Patterns/s) | DATA RATE (Giga Pixels/s) | MIRROR PITCH |
|---|---|---|---|---|---|
| DLP650LNIR - 0.65" WXGA NIR | 1280 × 800 | 12,500 | 10,811 | 12 | 10.8 μm |

### 7.3.1 DLPC410: Digital Controller for DLP Discovery 4100 Chipset

The DLPC410 chipset includes the DLPC410 controller which provides a high-speed LVDS data and control interface for DMD control. This interface is also connected to a second FPGA used to drive applications (not included in the chipset). The DLPC410 generates DMD and DLPA200 initialization and control signals in response to the inputs on the control interface.

For more information, see the DLPC410 data sheet (DLPS024).

### 7.3.2 DLPA200: DMD Micromirror Driver

DLPA200 micromirror driver provides the micromirror clocking pulse driver functions for the DMD. A single driver is required for DLP650LNIR DMD.

The DLPA200 is designed to work with multiple DLP chipsets. The DLPA200 contains 16 MBSRT output pins and all 16 are used with the DLP650LNIR chipset. For more information see the DLPC410 (DLPS024) and the DLPA200 data sheets (DLPS015).

### 7.3.3 DLPR410: PROM for DLP Discovery 4100 Chipset

The DLPC410 controller is configured at startup from the DLPR410 PROM. The contents of this PROM are fixed and cannot be altered. For more information, see the DLPR410 data sheet (DLPS027) and the DLPC410 data sheet (DLPS024).

### 7.3.4 DLP650LNIR: DLP 0.65 WXGA NIR 2xLVDS Series 450 DMD

#### *7.3.4.1 DLP650LNIR Chipset Interfaces*

This section describes the interface between the different components included in the chipset. For more information on component interfacing, see *Application Information*.

##### 7.3.4.1.1 DLPC410 Interface Description

###### *7.3.4.1.1.1 DLPC410 IO*

Table 4 describes the inputs and outputs of the DLPC410 related to the control of the DLP650LNIR DMD. For more details on these signals, see the DLPC410 data sheet (DLPS024).

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**Table 4. Input/Output Description**

| PIN NAME | DESCRIPTION | I/O |
|---|---|---|
| $\overline{\text{ARST}}$ | Asynchronous active low reset | I |
| CLKIN_R | Reference clock, 50 MHz | I |
| DIN_[A,B,C,D](15:0) | LVDS DDR input for data bus A,B,C,D (15:0) | I |
| DCLKIN[A,B,C,D] | LVDS inputs for data clock (400 MHz) on bus A, B, C, and D | I |
| DVALID[A,B,C,D] | LVDS input signals used to start write sequence for bus A, B, C, and D | I |
| ROWMD(1:0) | DMD row address and row counter control | I |
| ROWAD(10:0) | DMD row address pointer | I |
| BLK_AD(3:0) | DMD mirror block address pointer | I |
| BLK_MD(1:0) | DMD mirror block reset and clear command modes | I |
| PWR_FLOAT | Used to float DMD mirrors before complete loss of power | I |
| LOAD4 | Load4 mode enable [uses DLPC410 SPARE_0 input pin (AB21)] | I |
| DMD_TYPE(3:0) | DMD type in use | O |
| RST_ACTIVE | Indicates DMD mirror reset in progress | O |
| INIT_ACTIVE | Initialization in progress. | O |
| VLED0 | System “heartbeat” signal | O |
| VLED1 | Denotes initialization complete | O |

#### *7.3.4.1.1.2 Initialization*

The *INIT_ACTIVE* (Table 4) signal indicates that the DLP650LNIR, DLPA200, and DLPC410 are in an initialization state after power is applied. During this initialization period, the DLPC410 is initializing the DLP650LNIR and DLPA200 by setting all internal registers to their correct states. When this signal goes low, the system has completed initialization. System initialization takes approximately 220 ms to complete. Data and command write cycles should not be asserted during the initialization.

During initialization the user must send a training pattern to the DLPC410 on all data and DVALID lines to correctly align the data inputs to the data clock. For more information, see the interface training pattern information in the DLPC410 data sheet.

#### *7.3.4.1.1.3 DMD Device Detection*

The DLPC410 automatically detects the DMD type and device ID. DMD_TYPE (Table 4) is an output from the DLPC410 that contains the DMD information.

#### *7.3.4.1.1.4 Power Down*

To ensure long term reliability of the DLP650LNIR DMD, a shutdown procedure must be executed. Prior to power removal, assert the PWR_FLOAT (Table 4) signal and allow approximately 300 µs to assure the mirrors are in a flat state prior to power removal.

**NOTE**

Use PWR_FLOAT only when DC power is going to be removed from the DMD. When not powering down but it is desired to place the system in an idle (non-functioning) state, all applications benefit from operating the DMD near 50% landed on/off duty cycle. See section 3 (Duty Cycle Considerations) in application note DLPA052 - System Design Considerations Using TI DLP® Technology down to 400 nm.

### 7.3.4.1.2 DLPC410 to DMD Interface

#### *7.3.4.1.2.1 DLPC410 to DMD IO Description*

Table 5 lists the available controls and status pin names and their corresponding signal type, along with a brief functional description.


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**Table 5. DLPC410 to DMD I/O Pin Descriptions**

| PIN NAME | DESCRIPTION | I/O |
|---|---|---|
| DOUT_A[15,13,11,9,7,5,3,1] | 2xLVDS DDR output to DMD data bus A[15,13,11,9,7,5,3,1] | O |
| DOUT_B[15,13,11,9,7,5,3,1] | 2xLVDS DDR output to DMD data bus B[15,13,11,9,7,5,3,1] | O |
| DCLKOUT_[A,B] | 2xLVDS output to DMD data clock DCLKA and DCLKB | O |
| SCTRL_[A,B] | 2xLVDS DDR output to DMD data control buses A, and B | O |

#### *7.3.4.1.2.2 Data Flow*

Figure 12 shows the data traffic through the DLPC410. Special considerations are necessary when laying out the DLPC410 to allow best signal flow.

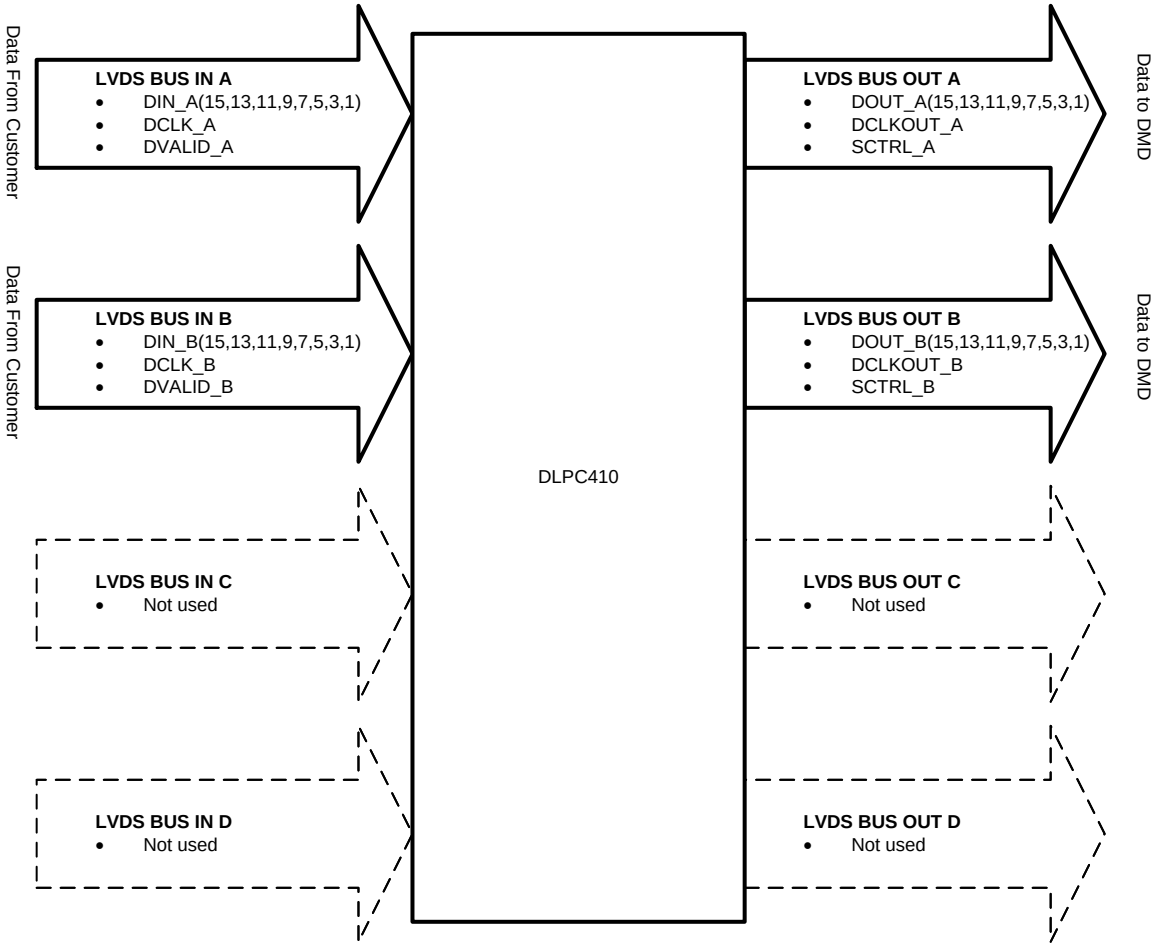



**Figure 12. DLPC410 Data Flow**

Two LVDS buses A and B transfer the data from the user to the DLPC410. Each bus has its own data clock that is input edge aligned with the data (DCLK). Each bus also has its own validation signal that qualifies the data input to the DLPC410 (DVALID).

Output LVDS buses A and B transfer data from the DLPC410 to the DLP650LNIR. The DLP650LNIR uses only the odd input signals of the output buses A and B.

Buses C and D are used with DMDs which have 64-bit wide data inputs only.

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#### 7.3.4.1.3 DLPC410 to DLPA200 Interface

##### *7.3.4.1.3.1 DLPA200 Operation*

The DLPA200 DMD micromirror driver is a mixed-signal application-specific integrated circuit (ASIC) that combines the necessary high-voltage power supply generation and micromirror clocking pulse functions for a family of DMDs. The DLPA200 is programmable and controllable to meet all current and anticipated DMD requirements.

The DLPA200 operates from a 12-V power supply input. For more detailed information on the DLPA200, see the DLPA200 data sheet.

##### *7.3.4.1.3.2 DLPC410 to DLPA200 IO Description*

The Serial Communications Port (SCP) is a full duplex, synchronous, character-oriented (byte) port that allows exchange of commands from the DLPC410 to the DLPA200. One SCP bus is used for the DLP650LNIR.

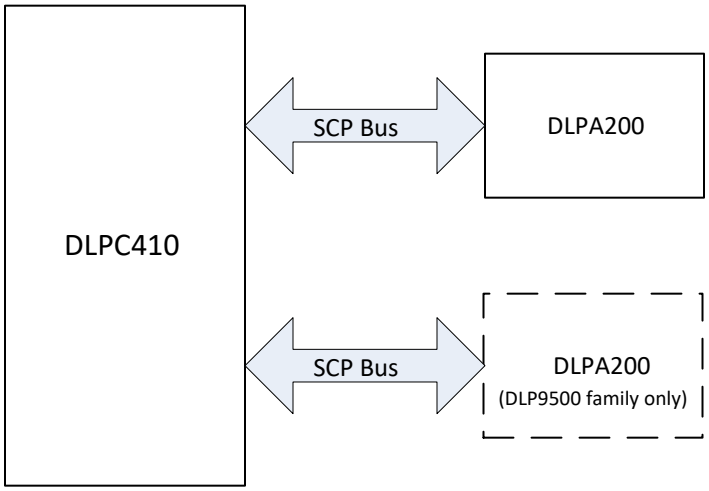



**Figure 13. Serial Port System Configuration**

Five signal lines are associated with the SCP bus: $\overline{\text{SCPEN}}$, SCPCK, SCPDI, SCPDO, and $\overline{\text{IRQ}}$.

Table 6 lists the available controls and status pin names and their corresponding signal type, along with a brief functional description.

**Table 6. DLPC410 to DLPA200 I/O Pin Descriptions**

| PIN NAME | DESCRIPTION | I/O |
|---|---|---|
| $\overline{\text{A_SCPEN}}$ | Active-low chip select for DLPA200 serial bus | O |
| A_STROBE | DLPA200 control signal strobe | O |
| A_MODE(1:0) | DLPA200 mode control | O |
| A_SEL(1:0) | DLPA200 select control | O |
| A_ADDR(3:0) | DLPA200 address control | O |
| $\overline{\text{B_SCPEN}}$ | Active-low chip select for DLPA200 serial bus (2) | O |
| B_STROBE | DLPA200 control signal strobe (2) | O |
| B_MODE(1:0) | DLPA200 mode control | O |
| B_SEL(1:0) | DLPA200 select control | O |
| B_ADDR(3:0) | DLPA200 address control | O |


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The DLPA200 provides a variety of output options to the DMD by selecting logic control inputs: MODE[1:0], SEL[1:0] and reset group address A[3:0] (Table 6). The MODE[1:0] input determines whether a single output, two outputs, four outputs, or all outputs, are selected. Output levels (VBIAS, VOFFSET, or VRESET) are selected by SEL[1:0] pins. Selected outputs are tri-stated on the rising edge of the STROBE signal and latched to the selected voltage level after a break-before-make delay. Outputs remain latched at the last micromirror clocking pulse waveform level until the next micromirror clocking pulse waveform cycle.

#### 7.3.4.1.4 DLPA200 to DLP650LNIR Interface

##### *7.3.4.1.4.1 DLPA200 to DLP650LNIR Interface Overview*

The DLPA200 generates three voltages: VBIAS, VRESET, and VOFFSET that are supplied to the DMD MBRST lines in various sequences through the micromirror clocking pulse driver function. VOFFSET is also supplied directly to the DMD as VCC2. A fourth DMD power supply, VCC, is supplied directly to the DMD by regulators.

The function of the micromirror clocking pulse driver is to switch selected outputs in patterns between the three voltage levels (VBIAS, VRESET and VOFFSET) to generate one of several micromirror clocking pulse waveforms. The order of these micromirror clocking pulse waveform events is controlled externally by the logic control inputs and timed by the STROBE signal. DLPC410 automatically detects the DMD type and then uses the DMD type to determine the appropriate micromirror clocking pulse waveform.

A direct micromirror clocking pulse operation causes a mirror to transition directly from one latched state to the next. The address must already be set up on the mirror electrodes when the micromirror clocking pulse is initiated. Where the desired mirror display period does not allow for time to set up the address, a micromirror clocking pulse with release can be performed. This operation allows the mirror to go to a relaxed state regardless of the address while a new address is set up, after which the mirror can be driven to a new latched state.

A mirror in the relaxed state typically reflects light into a system collection aperture and can be thought of as *off* although the light is likely to be more than a mirror latched in the *off* state. Carefully evaluate the impact of relaxed mirror conditions on optical performance.

### 7.3.5 Measurement Conditions

The data sheet provides timing at the device pin. For output timing analysis, the tester pin electronics and its transmission line effects must be taken into account. Figure 14 shows an equivalent test load circuit for the output under test. The load capacitance value stated is only for characterization and measurement of AC timing signals. This load capacitance value does not indicate the maximum load the DMD is capable of driving. All rise and fall transition timing parameters are referenced to $V_{IL(max)}$ and $V_{IH(min)}$ for input clocks, $V_{OL(max)}$ and $V_{OH(min)}$ for output clocks.

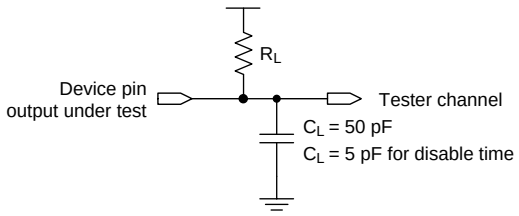



**Figure 14. Test Load Circuit for AC Timing Measurements**

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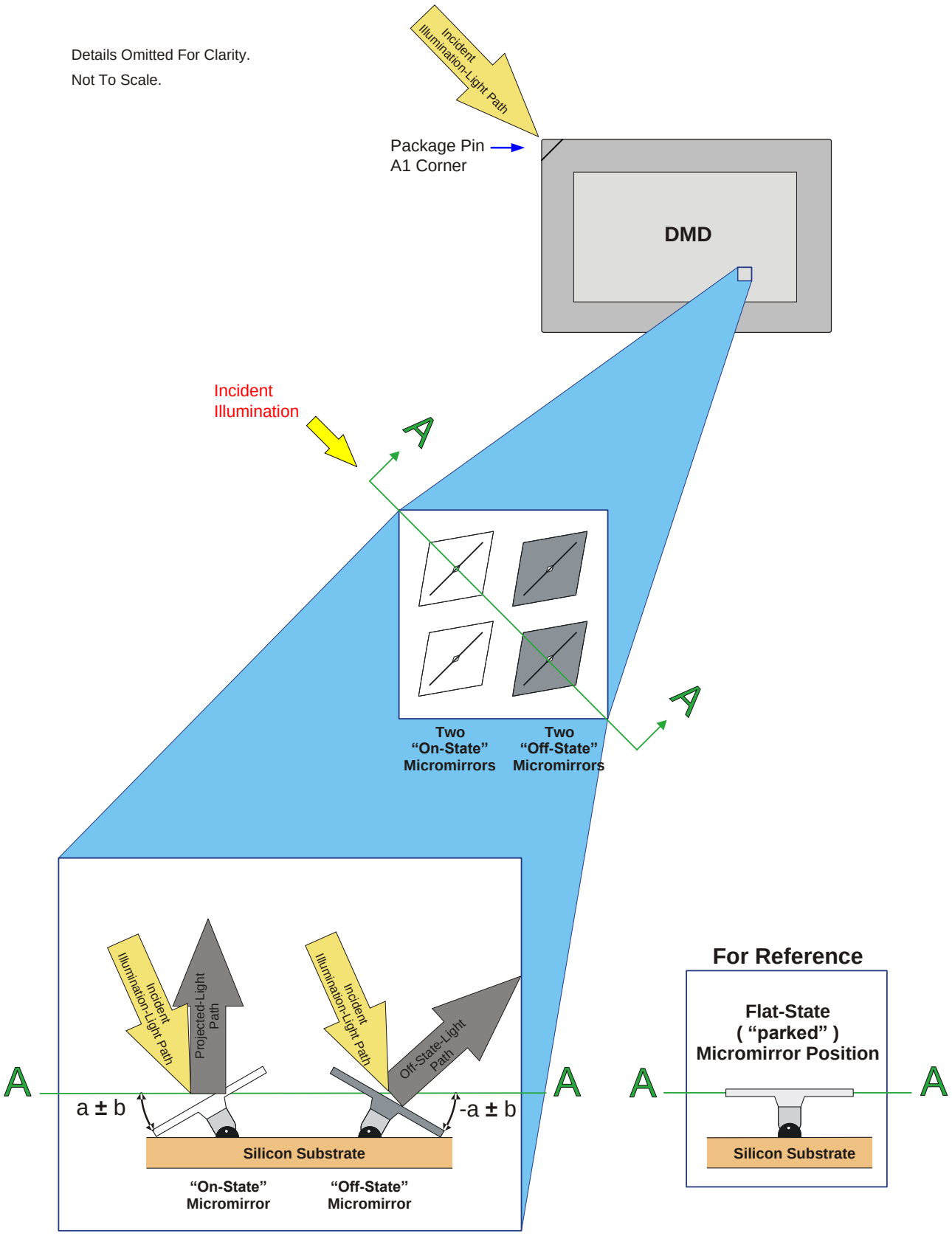



**Figure 15. Micromirror Landed Positions and Light Paths**


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## 7.4 Device Operational Modes

### 7.4.1 DMD Block Modes

When controlled by the DLPC410 controller in conjunction with the DLPA200 driver, the DLP650LNIR can be operated in four unique Block Modes. The DLP650LNIR is vertically segmented into 16 horizontal blocks, each 50 rows tall. Figure 16, Figure 17, Figure 18, and Figure 19 show how the DLPC410 can load and display an image using the different DMD Block Modes.

There are four Block Modes that determine which blocks are "reset" when a Micromirror Clocking Pulse command is issued:

- Single block mode
- Dual block mode
- Quad block mode
- Global mode

#### *7.4.1.1 Single Block Mode*

In Single Block Mode, any single block can be loaded with new data and then "reset" to its new mirror mechanical state when a Mirror Clocking Pulse is issued. This can be performed in any block order as long as the certain timing restrictions are met.

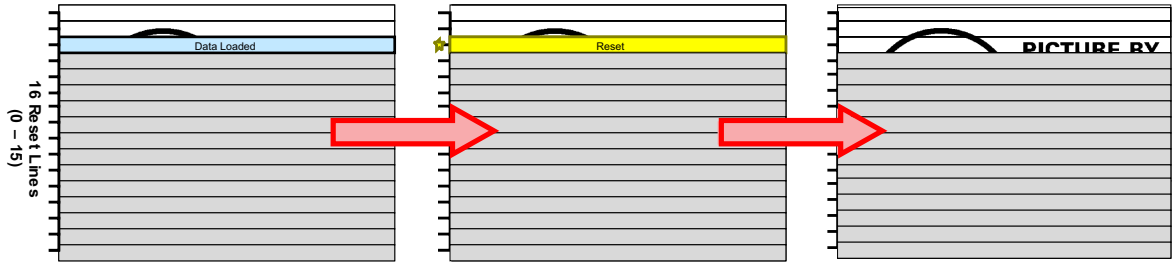



**Figure 16. Single Block Mode Diagram**

#### *7.4.1.2 Dual Block Mode*

In Dual Block Mode, the reset blocks of the DMD are grouped in to pairs such that the Mirror Clocking Pulse causes a pair of the DMD blocks to transition to their new states. In this mode, there are eight dual reset blocks paired together as follows (0-1), (2-3), (4-5), (6-7), (8-9), (10-11), (12-13), (14-15). Each dual group can be randomly addressed and reset. These pairs can be reset in any order by presenting the correct block mode commands to the DLPC410. After data is loaded into both groups, a pair can be reset to transfer the information to the mechanical state of the mirrors. Then another pair can be loaded and reset, etc.

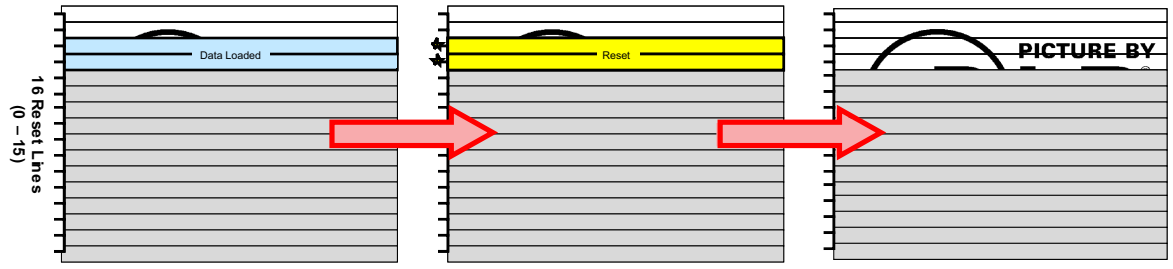



**Figure 17. Dual Block Mode Diagram**

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## Device Operational Modes (continued)

### 7.4.1.3 Quad Block Mode

In Quad Block Mode, blocks of four are grouped together to receive the Mirror Clocking Pulse at the same time. In this mode, there are be 4 groups of four block each as follows (0-3), (4-7), (8-11) and (12-15). Each quad group can be randomly addressed and reset. After a quad group is loaded, it can be reset to transfer the information to the mechanical state of the mirrors.

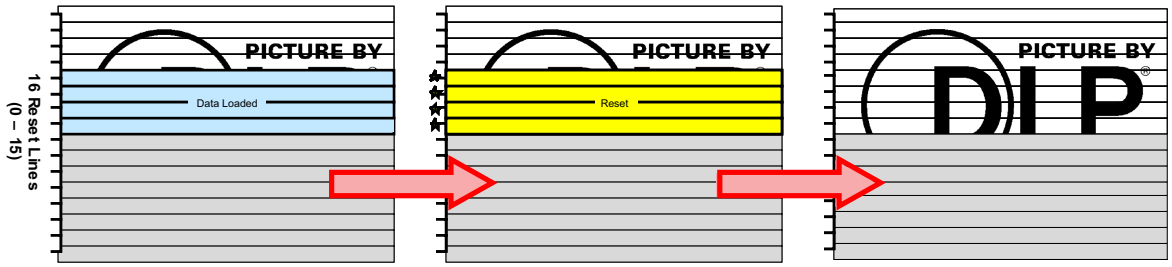



**Figure 18. Quad Block Mode Diagram**

### 7.4.1.4 Global Mode

In global mode, all 16 reset blocks are grouped into a single large group and reset together. The entire DMD must be loaded with the desired data before issuing a Global Reset to transfer the information to the mechanical state of the mirrors.

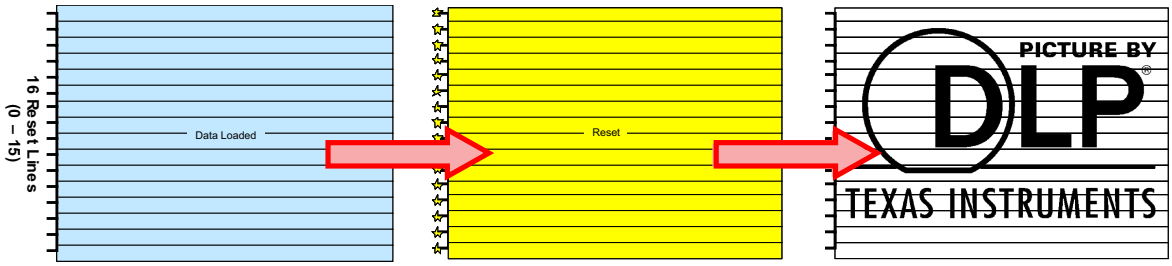



**Figure 19. Global Mode Diagram**

### 7.4.2 DMD Load4 Mode

Load4 Mode is a special data loading function of the DLP650LNIR DMD which is supported by the DLPC410 Controller. This mode allows the DLPC410 (an hence, the end user) to load the DMD faster at the expense of vertical resolution. In Load4 Mode, the device loads each horizontal line of data presented by the DLPC410 to the DLP650LNIR into 4 consecutive rows of the DMD. For example, assuming the DLPC410 presents the first row of new data to row 0 of the DMD, If Load4 is enabled then the device loads this single row of new input data into each of the first 4 rows (0-3) of the DMD. The device loads the next row presented to the DMD into the next 4 rows of the DMD (4-7), and so on.

Take precautions when using Load4 mode with the DLP650LNIR DMD, as each reset block of this DMD is 50 rows which is not evenly divisible by 4. Therefore, loading the last two rows of an even number block concurrently loads the first two rows in the subsequent odd number block. Conversely, to load an odd block, the last two rows of the preceding even number block need to be loaded first. See the DLPC410 datasheet for more information on how Load4 mode operates.


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## 7.5 Feature Description

### 7.5.1 Power Interface

The DLP650LNIR DMD requires three DC input voltages: $V_{CC}$, $V_{CCI}$, and $V_{CC2}$. It is typically allowable for $V_{CC}$ and $V_{CCI}$ to be provided by the same 3.3VDC power source. $V_{CC2}$ is created by the DLPA200 DMD micromirror driver. The DLPA200 also creates other voltages ($V_{BIAS}$, $V_{OFFSET}$, and $V_{RESET}$) which it uses internally in creating the Mirror Clocking Pulses provided to the DMD on the MBRST signals inputs. The Mirror Clocking Pulses (resets) are provided to the DMD to facilitate the micromirror transitions from one state to the next state.

### 7.5.2 Timing

The data sheet provides timing at the device pin. For output timing analysis, the tester pin electronics and its transmission line effects must be taken into account. Figure 5 shows an equivalent test load circuit for the output under test. Timing reference loads are not intended as a precise representation of any particular system environment or depiction of the actual load presented by a production test. Use IBIS or other simulation tools to correlate the timing reference load to a system environment. The load capacitance value stated is only for characterization and measurement of AC timing signals. This load capacitance value does not indicate the maximum load the device is capable of driving.

## 7.6 Optical Interface and System Image Quality Considerations

**NOTE**

TI assumes no responsibility for image quality artifacts or DMD failures caused by optical system operating conditions exceeding limits described previously.

### 7.6.1 Optical Interface and System Image Quality

TI assumes no responsibility for end-equipment optical performance. Achieving the desired end-equipment optical performance involves making trade-offs between numerous component and system design parameters. Optimizing system optical performance and image quality strongly relate to optical system design parameter trades. Although it is not possible to anticipate every conceivable application, projector image quality and optical performance is contingent on compliance to the optical system operating conditions described in the following sections.

### 7.6.2 Numerical Aperture and Stray Light Control

Maintain the angle defined by the numerical aperture of the illumination optics at the DMD optical area to be the same angle implemented for the projection optics. Do not exceed the nominal device mirror tilt angle unless appropriate apertures are added in the illumination, projection pupils, or both to block out flat-state and stray light from the projection lens. The mirror tilt angle defines DMD capability to separate the *ON* optical path from any other light path, including undesirable flat-state specular reflections from the DMD window, DMD border structures, or other system surfaces near the DMD such as prism or lens surfaces. If the numerical aperture exceeds the mirror tilt angle, or if the projection numerical aperture angle is more than two degrees larger than the illumination numerical aperture angle, objectionable artifacts in the display's border and/or active area could occur.

### 7.6.3 Pupil Match

TI recommends the exit pupil of the illumination is nominally centered within 2° (two degrees) of the entrance pupil of the projection optics. Misalignment of pupils can create objectionable artifacts in the display's border and/or active area, which may require additional system apertures to control, especially if the numerical aperture of the system exceeds the pixel tilt angle.

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## Optical Interface and System Image Quality Considerations (continued)

### 7.6.4 Illumination Overfill

The active area of the device is surrounded by an aperture on the inside DMD window surface that masks structures of the DMD device assembly from normal view. The aperture is sized to anticipate several optical operating conditions. Overfill light illuminating the window aperture can create artifacts from the edge of the window aperture opening and other surface anomalies that may be included in the projected image. To reduce DMD heating when applying high incident flux levels to the DMD in high power applications, design the illumination optics to limit light flux incident anywhere outside the active array to nearly zero percent. For lower incident power levels, depending on the optical architecture of a particular system, the acceptability levels of overfill light must be determined by the user as it relates to a specific application. In most cases it is almost always held to zero.

## 7.7 Micromirror Temperature Calculations

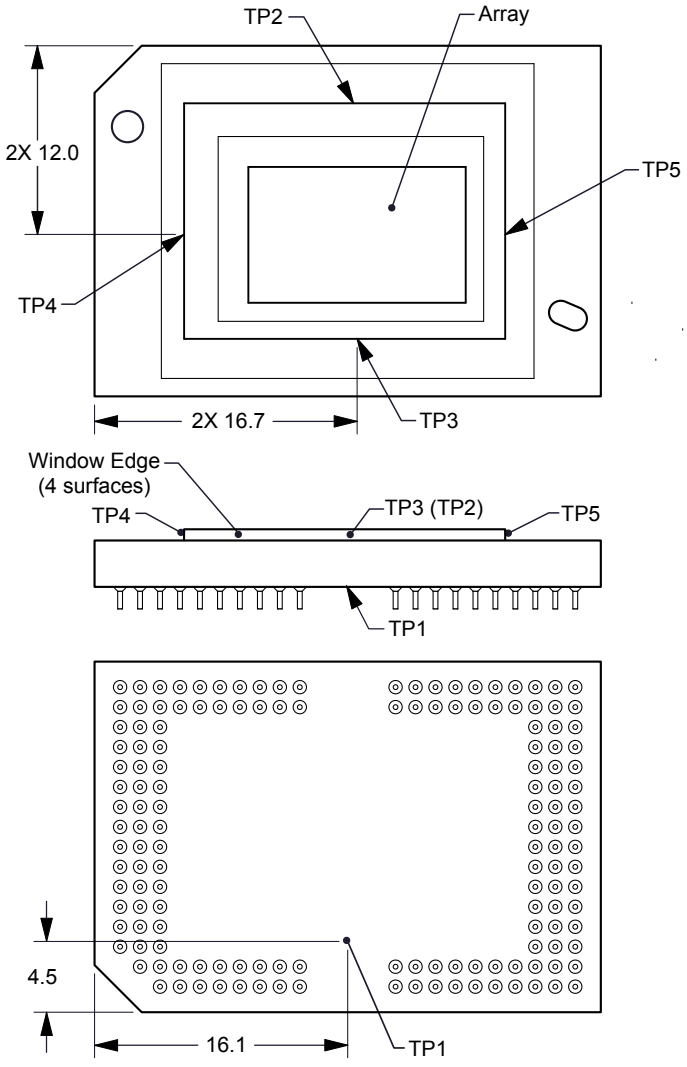



**Figure 20. DMD Thermal Test Points**


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## Micromirror Temperature Calculations (continued)

The DMD Micromirror temperature cannot be measured directly, therefore it must be computed analytically from:

- the measurement point on the outside of the package
- the silicon-to-ceramic thermal resistance
- the mirror-to-silicon thermal resistance
- the internally generated electrical power
- and the illumination heat load

The relationship between mirror temperature and the reference ceramic temperature (thermal test TP1 in Figure 20) is provided by the following equations:

$$T_{MIRROR} = T_{CERAMIC} + Delta_T_{SILICON\text{-}TO\text{-}CERAMIC} + Delta_T_{MIRROR\text{-}TO\text{-}SILICON}$$

$$Delta_T_{SILICON\text{-}TO\text{-}CERAMIC} = Q_{SILICON} \times R_{SILICON\text{-}TO\text{-}CERAMIC}$$

$$Delta_T_{MIRROR\text{-}TO\text{-}SILICON} = Q_{MIRROR} \times R_{MIRROR\text{-}TO\text{-}SILICON}$$

$$Q_{SILICON} = Q_{ELECTRICAL} + (\alpha_{DMD} \times Q_{INCIDENT})$$

$$Q_{MIRROR} = Q_{INCIDENT_MIRROR} \times [FF_{OFF\text{-}STATE_MIRROR} \times (1 - MR)] \quad (1)$$

$$\alpha_{DMD} = [FF_{OFF\text{-}STATE_MIRROR} \times (1\text{-}MR)] + [1\text{-}FF_{OFF\text{-}STATE\text{-}MIRROR}] + [2 \times \alpha_{WINDOW}] \quad (2)$$

where:

- $T_{MIRROR}$ = computed micromirror temperature (°C)
- $T_{CERAMIC}$ = measured ceramic temperature (°C) (TP1 location)
- $Delta_T_{SILICON\text{-}TO\text{-}CERAMIC}$ = temperature rise of silicon above ceramic test point TP1
- $Delta_T_{MIRROR\text{-}TO\text{-}SILICON}$ = temperature rise of an individual mirror above the silicon (°C)
- $R_{SILICON\text{-}TO\text{-}CERAMIC}$ = thermal resistance, silicon die to ceramic TP1 (°C/Watt) as specified in Thermal Information
- $R_{MIRROR\text{-}TO\text{-}SILICON}$ = thermal resistance, individual mirror to silicon die (°C/Watt) as specified in Thermal Information
- $Q_{SILICON}$ = total DMD power (electrical + absorbed) on the silicon (Watts)
- $Q_{MIRROR}$ = absorbed heat load on a single mirror (Watts)
- $Q_{ELECTRICAL}$ = nominal electrical power (Watts)
- $Q_{INCIDENT}$ = total incident optical power to DMD (Watts)
- $Q_{INCIDENT_MIRROR}$ = Incident optical power on an individual mirror (Watts)
- $\alpha_{DMD}$ = absorptivity of DMD
- $\alpha_{WINDOW}$ = absorptivity of DMD window (single pass)
- $FF_{OFF\text{-}STATE\text{-}MIRROR}$ = DMD off-state mirror fill factor
- MR = DMD mirror reflectivity

The electrical power dissipation of the DMD is variable and depends on the voltages, data rates and operating frequencies. The absorbed power from the illumination source is variable and depends on the operating state of the micromirrors and the intensity of the light source. The equations shown above are valid for a system operating at 1064 nm with 100% of the illumination contained within the 1280 × 800 active array mirrors. Silicon-to-ceramic thermal resistance assumes the entire active micromirror array is uniformly illuminated.

**NOTE**

Incident irradiation that concentrates on a subset of the micromirror array, results in an increase in effective package thermal resistance.

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## Micromirror Temperature Calculations (continued)

### 7.7.1 Sample Calculation 1: Uniform Illumination of Entire DMD Active Array (1280 × 800 pixels)

This calculation assumes that the entire DMD active array (1280 × 800) mirrors is uniformly illuminated with zero overfill falling outside the Pond of Mirrors pixel border. The highest DMD temperatures typically occur when the DMD mirrors are in the off-state (–12° landed) position. Therefore, the off-state fill factor calculates the worst case mirror temperature. Calculate the mirror temperatures to assess the viability of the illumination conditions.

- $FF_{OFF\text{-}STATE\text{-}MIRROR}$ = 75.3%
- MR @ 1064 nm = 94%
- $\alpha_{WINDOW}$@ 1064 nm = 0.7%
- $R_{MIRROR\text{-}TO\text{-}SILICON}$ = 3.39E5 °C/Watt
- $R_{SILICON\text{-}TO\text{-}CERAMIC}$ = 0.5 °C/Watt
- Array Resolution = 1280 × 800
- $T_{CERAMIC}$ = 30.0°C (measured)
- $Q_{INCIDENT}$ = 160 W (measured)
- $Q_{ELECTRICAL}$ = 1.8 W

$\alpha_{DMD}$ = [0.753 × (1-0.94)] + (1 - 0.753) + (2 × 0.007) = 0.31

$Q_{SILICON}$ = 1.8 W + (0.31 × 160 W) = 51.4 W

$Q_{MIRROR}$ = [(160W / (1280 × 800)] × 0.753 × (1 - 0.94) = 7.06E-6 W

$Delta_T_{SILICON\text{-}TO\text{-}CERAMIC}$ = 51.4 W × 0.5°C/W= 25.7°C

$Delta_T_{MIRROR\text{-}TO\text{-}SILICON}$ = 7.06E-6 W × 3.39E5 °C/W= 2.4°C

$T_{MIRROR}$ = 30.0°C + 25.7 + 2.4°C = **58.1°C**

### 7.7.2 Sample Calculation 2: Partial DMD Active Array Illumination with Non-uniform Illumination Peak

This calculation assumes that only a subsection of the DMD active array 960 × 475 pixels in size is (non-uniformly) illuminated. This calculation assumes the illuminated area is in the center of the DMD. Non-centered area can affect the value of $R_{SILICON\text{-}TO\text{-}CERAMIC}$. If the application requires offsetting the illumination on the DMD, contact TI for more information on how to assess $R_{SILICON\text{-}TO\text{-}CERAMIC}$. As in Sample Calculation 1, the off-state fill factor can be used to assess the highest temperatures that can occur. Calculate the mirror temperatures which occur at the highest illumination intensities to assess the viability of the illumination conditions.

- $FF_{OFF\text{-}STATE\text{-}MIRROR}$ = 75.3%
- MR @ 1064 nm = 94%
- $\alpha_{WINDOW}$@ 1064 nm = 0.7%
- $R_{MIRROR\text{-}TO\text{-}SILICON}$ = 3.39E5 °C/Watt
- $R_{SILICON\text{-}TO\text{-}CERAMIC}$ = 0.9 °C/Watt (higher than previous example due to reduced illumination area)
- Pixel Size = 10.8 µm = 0.00108 cm (square)
- $T_{CERAMIC}$ = 30.0°C (measured)
- $Q_{INCIDENT}$ = 60 W (measured)
- $Q_{ELECTRICAL}$ = 1.8 W
- Peak Irradiance = 500 W/cm$^2$ (measured)

$\alpha_{DMD}$ = [0.753 × (1 - 0.94)] + (1 - 0.753) + (2 × 0.007) = 0.31

$Q_{SILICON}$ = 1.8 W + (0.31 × 60 W) =20.4 W

$Q_{INCIDENT_MIRROR}$ = Peak Irradiance (W/cm$^2$) × Pixel Area (cm$^2$) = [500 W/cm$^2$ × (0.00108 cm)$^2$ ] = 5.832E-4 W

$Q_{MIRROR}$ = 5.832E-4 W × 0.753 × (1 - 0.94) = 2.64E-5 W

$Delta_T_{SILICON\text{-}TO\text{-}CERAMIC}$ = 20.4 W × 0.9°C/W = 18.4°C

$Delta_T_{MIRROR\text{-}TO\text{-}SILICON}$ = 2.64E-5 W × 3.39E5°C/W= 8.9°C

$T_{MIRROR}$ = 30.0°C + 18.4°C + 8.9°C = **57.3°C**


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## 7.8 Micromirror Landed-On/Landed-Off Duty Cycle

### 7.8.1 Definition of Micromirror Landed-On/Landed-Off Duty Cycle

The micromirror landed-on/landed-off duty cycle (landed duty cycle) denotes the amount of time (as a percentage) that an individual micromirror is landed in the On state versus the amount of time the same micromirror is landed in the Off state.

As an example, a landed duty cycle of 100/0 indicates that the referenced pixel is in the On state 100% of the time (and in the Off state 0% of the time); whereas 0/100 would indicate that the pixel is in the Off state 100% of the time. Likewise, 50/50 indicates that the pixel is On 50% of the time and Off 50% of the time.

Note that when assessing landed duty cycle, the time spent switching from one state (ON or OFF) to the other state (OFF or ON) is considered negligible and is thus ignored.

Because a micromirror can be landed in only one of the two available states (on or off), the two numbers (percentages) always add to 100.

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## Micromirror Landed-On/Landed-Off Duty Cycle (continued)

### 7.8.2 Landed Duty Cycle and Useful Life of the DMD

Knowing the long-term average landed duty cycle (of the end product or application) is important because subjecting all (or a portion) of the DMD micromirror array (also called the active array) to an asymmetric landed duty cycle for a prolonged period of time can reduce usable life of the DMD.

Note that it is the symmetry and asymmetry of the landed duty cycle that are of relevance. The symmetry of the landed duty cycle is determined by how close the two numbers (percentages) are to being equal. For example, a landed duty cycle of 50/50 is perfectly symmetrical whereas a landed duty cycle of 100/0 or 0/100 is perfectly asymmetrical.

### 7.8.3 Landed Duty Cycle and Operational DMD Temperature

Operational DMD Temperature and Landed Duty Cycle interact to affect the useable life of the DMD, and this interaction can be exploited to reduce the impact that an asymmetrical Landed Duty Cycle has on the useable life of the DMD. This is quantified in the de-rating curve shown in Figure 2. The importance of this curve is that:

- All points along this curve represent the same usable life.
- All points above this curve represent lower usable life (and the further away from the curve, the lower the usable life).
- All points below this curve represent higher usable life (and the further away from the curve, the higher the usable life).

In practice, this curve specifies the Maximum Operating DMD Temperature at a given long-term average Landed Duty Cycle.

### 7.8.4 Estimating the Long-Term Average Landed Duty Cycle of a Product or Application

During a given period of time, the Landed Duty Cycle of a given pixel follows from the image content being displayed by that pixel.

For example, in the simplest case, when displaying pure-white on a given pixel for a given time period, that pixel experiences a 100/0 Landed Duty Cycle during that time period. Likewise, when displaying pure-black, the pixel experiences a 0/100 Landed Duty Cycle.

Between the two extremes, the Landed Duty Cycle tracks one-to-one with the gray scale value, as shown in Table 7.

**Table 7. Grayscale Value and Landed Duty Cycle**

| GRAYSCALE VALUE | LANDED DUTY CYCLE |
|---|---|
| 0% | 0/100 |
| 10% | 10/90 |
| 20% | 20/80 |
| 30% | 30/70 |
| 40% | 40/60 |
| 50% | 50/50 |
| 60% | 60/40 |
| 70% | 70/30 |
| 80% | 80/20 |
| 90% | 90/10 |
| 100% | 100/0 |


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# 8 Application and Implementation

**NOTE**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 8.1 Application Information

The DLP650LNIR devices require they be coupled with the DLPC410 controller to provide a reliable solution for many different applications. The DMDs are spatial light modulators which reflect incoming light from an illumination source to one of two directions, with the primary direction being into a projection collection optic. Each application is derived primarily from the optical architecture of the system and the format of the data coming into the DLPC410. Applications of interest include 3D Printing, Selective Laser Sintering (SLS), Dynamic Grayscale Laser Marking, Industrial Printing, Flexographic Printing, Digital Plate making, and Repair and Ablation.

### 8.1.1 Device Description

The DLP650LNIR WXGA chipset offers developers a convenient way to design a wide variety of industrial, medical, telecom and advanced display applications by delivering maximum flexibility in formatting data, sequencing data, and light patterns.

The DLP650LNIR WXGA chipset includes the following four components: DMD Digital Controller (DLPC410), EEPROM (DLPR410), DMD Micromirror Driver (DLPA200), and a DMD (DLP650LNIR).

**DLPC410** Digital Controller for DLP Discovery 4100 chipset

- Provides high speed LVDS data and control interface to the DLP650LNIR.
- Drives mirror clocking pulse and timing information to the DLPA200.
- Supports random row addressing.

**DLPR410** PROM for DLP Discovery 4100 chipset

- Contains startup configuration information for the DLPC410.

**DLPA200** DMD Micromirror Driver

- Generates Micromirror Clocking Pulse control (sometimes referred to as a "Reset") of DMD mirrors.

**DLP650LNIR** DLP 0.65 WXGA NIR 2xLVDS DMD

- Steers light in two digital positions (+12º and -12º) using 1280 × 800 micromirror array of aluminum mirrors.

**Table 8. DLPC410 Chipset Configuration for 0.65 WXGA NIR Chipset**

| QUANTITY | TI PART | DESCRIPTION |
|---|---|---|
| 1 | DLP650LNIR | DLP 0.65 WXGA NIR 2xLVDS DMD |
| 1 | DLPC410 | Digital Controller for DLP Discovery 4100 chipset |
| 1 | DLPR410 | PROM for DLP Discovery 4100 chipset |
| 1 | DLPA200 | DMD Micromirror Driver |

Reliable function and operation of DLP650LNIR WXGA chipsets require the components be used in conjunction with each other. This document describes the proper integration and use of the DLP650LNIR WXGA chipset components.

The DLP650LNIR WXGA chipset can be combined with a user programmable Application FPGA (not included) to create high performance systems.

## 8.2 Typical Application

A typical embedded system application using the DLPC410 controller and DLP650LNIR is shown in Figure 21. In this configuration, the DLPC410 controller supports input from an FPGA. The FPGA sends low-level data to the controller, enabling the system to be highly optimized for low latency and high speed.

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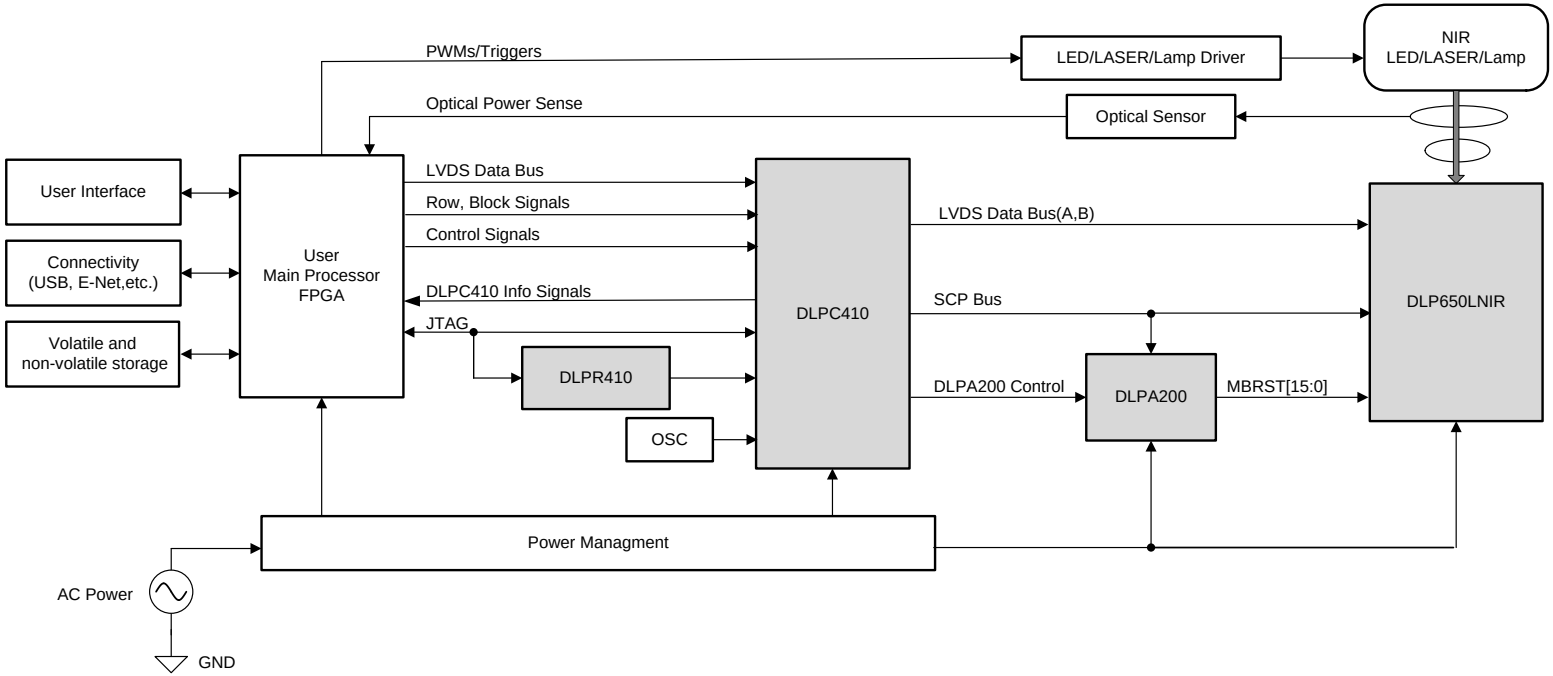



**Figure 21. DLPC410 and DLP650LNIR Embedded Example Block Diagram**


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### 8.2.1 Design Requirements

All applications using the DLP650LNIR WXGA chipset require both the controller and the DMD components for operation. The system also requires an external parallel flash memory device loaded with the DLPC410 Configuration and Support Firmware. The chipset has several system interfaces and requires some support circuitry. The following interfaces and support circuitry are required:

- DLPC410 System Interfaces:
  - Control Interface
  - Trigger Interface
  - Input Data Interface
  - Illumination Interface
  - Reference Clock
- DLP650LNIR Interfaces:
  - DLPC410 to DLP650LNIR Digital Data
  - DLPC410 to DLP650LNIR Control Interface
  - DLPC410 to DLP650LNIR Micromirror Reset Control Interface
  - DLPC410 to DLPA200 Micromirror Driver
  - DLPA200 to DLP650LNIR Micromirror Reset

### 8.2.2 Detailed Design Procedure

The DLP650LNIR DMD is well suited for Near-Infrared (NIR) light applications requiring fast, spatially programmable light patterns using the micromirror array. See the to see the connections between the DLP650LNIR DMD, the DLPC410 digital controller, the DLPR410 EEPROM, and the DLPA200 DMD micromirror drivers. See the Figure 21 for an application example. Follow the *Layout Guidelines* for reliability.

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# 9 Power Supply Recommendations

Repeated failure to adhere to the prescribed power-up and power-down procedures may affect device reliability. The DLP650LNIR power-up and power-down procedures are defined by the DLPC410 data sheet (DLPS024). These procedures must be followed to ensure reliable operation of the device.


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# 10 Layout

## 10.1 Layout Guidelines

The DLP650LNIR is a component of a chipset that is controlled by the DLPC410 in conjunction with the DLPA200. These guidelines refer to a PCB board with these components.

A target impedance of 50 Ω for single-ended signals and 100 Ω between LVDS signals is specified for all signal layers.

### 10.1.1 Impedance Requirements

Make sure to route signals to have a matched impedance of 50 Ω ±10% except for LVDS differential pairs (D_Xnn, DCLK_Xn, and SCTRL_Xn). Match the differential pairs to 100 Ω ±10% across each pair.

### 10.1.2 PCB Signal Routing

When designing a PCB for the DLP650LNIR controlled by the DLPC410 in conjunction with the DLPA200, the following are recommended:

Make sure that signal trace corners are no sharper than 45°. Make sure that adjacent signal layers have the predominate traces routed orthogonal to each other. TI recommends that critical signals be hand routed in the following order: DMD (LVDS signals), then DLPA200 signals.

TI does not recommend signal routing on power or ground planes.

TI does not recommend ground plane slots.

Make sure that high-speed signal traces do not cross over slots in adjacent power and/or ground planes.

**Table 9. Important Signal Trace Constraints**

| SIGNAL | CONSTRAINTS |
|---|---|
| LVDS (D_Xnn, DCLK_xn, and SCTRL_xn) | P-to-N data, clock, and SCTRL: <10 mils (0.25 mm); Pair-to-pair <10 mils (0.25 mm); Bundle-to-bundle <2000 mils (50 mm, for example D_Ann to D_Bnn)<br>Trace width: 4 mil (0.1 mm)<br>Trace spacing: In ball field – 4 mil (0.11 mm); PCB etch – 14 mil (0.36 mm)<br>Maximum recommended trace length <6 inches (150 mm) |

**Table 10. Power Trace Widths and Spacing**

| SIGNAL NAME | MINIMUM TRACE WIDTH | MINIMUM TRACE SPACING | LAYOUT REQUIREMENTS |
|---|---|---|---|
| GND | Maximize | 5 mil (0.13 mm) | Maximize trace width to connecting pin as a minimum |
| VCC, VCC2 | 20 mil (0.51 mm) | 10 mil (0.25 mm) | |
| MBRST[15:0] | 11 mil (0.23 mm) | 15 mil (0.38 mm) | |

### 10.1.3 Fiducials

Make sure that the fiducials for automatic component insertion are 0.05-inch copper with a 0.1-inch cutout (antipad). Fiducials for optical auto insertion are placed on three corners of both sides of the PCB.

### 10.1.4 DMD Interface

The digital interface from the DLPC410 to the DMD are LVDS signals that run at clock rates up to 400 MHz. Data is clocked into the DMD on both the rising and falling edge of the clock, so the data rate is 800 MHz. Make sure the LVDS signals have 100 Ω differential impedance. Make sure the differential signals are length-matched and are as short as possible. Parallel termination at the LVDS receiver is in the DMD; therefore, on board termination is not necessary.

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#### 10.1.4.1 Trace Length Matching

The DLPC410 DMD data signals require precise length matching. Make sure differential signals have impedance of 100 Ω (with 5% tolerance). It is important that the propagation delays are matched. The maximum differential pair uncoupled length is 100 mils with a relative propagation delay of ±25 mil between the p and n. Matching all signals exactly maximizes the channel margin. The signal path through all boards, flexible cables and internal DMD routing must be considered in this calculation.

### 10.1.5 DLP650LNIR Decoupling

Make sure to distribute general decoupling capacitors for the DLP650LNIR around the PCB and place them to minimize the distance from device voltage and ground pads. Each decoupling capacitor (0.1 µF recommended) needs vias directly to the ground and power planes. Via sharing between components (discreet or integrated) is discouraged. Tie the power and ground pads of the DLP650LNIR to the voltage and ground planes with their own vias.

#### 10.1.5.1 Decoupling Capacitors

Place decoupling capacitors so that they minimize the distance from the decoupling capacitor to the supply and ground pin of the component. Follow these specific guidelines:

- Locate the supply voltage pin of the capacitor close to the DMD supply voltage pin(s). The decoupling capacitor needs vias to ground and voltage planes. The DMD can be connected directly to the decoupling capacitor (no via) if the trace length is less than 0.1 inch. Otherwise, tie the component to the voltage or ground plane through separate vias.
- Make sure that the trace lengths of the voltage and ground connections for decoupling capacitors and components is less than 0.1 inch to minimize inductance.
- Make the trace width of the power and ground connection to decoupling capacitors and components as wide as possible to minimize inductance.
- Connecting decoupling capacitors to ground and power planes through multiple vias can reduce inductance and improve noise performance.
- Decoupling performance can be improved by utilizing low ESR and low ESL capacitors.

### 10.1.6 VCC and VCC2

Connect the VCC pins of the DMD directly to the DMD VCC plane. Distribut the decoupling for the VCC around the DMD and placed to minimize the distance from the voltage and ground pads. Each decoupling capacitor needs vias directly connected to the ground and power planes. Tie the VCC and GND pads of the DMD to the VCC and ground planes with their own vias.

The VCC2 voltage can be routed to the DMD as a wide trace. Place decoupling capacitors to minimize the distance from the VCC2 and ground pads of the DMD. Use wide etch from the decoupling capacitors to the DMD connection to reduce inductance and improves decoupling performance.

### 10.1.7 DMD Layout

See the respective sections in this data sheet for package dimensions, timing and pin out information.

### 10.1.8 DLPA200

The DLPA200 driver generates the micromirror clocking pulses for the DMD. Route the DMD-drive outputs from the DLPA200 (MBRST[15:0] with a minimum trace width of 11 mil and a minimum spacing of 15 mil. Route the VCC and VCC2 traces from the output capacitors to the DLPA200 with a minimum trace width and spacing of 11 mil and 15 mil, respectively. See the DLPA200 customer data sheet for mechanical package and layout information.

## 10.2 Layout Example

For LVDS (and other differential signal) pairs and groups, it is important to match trace lengths. In the area of the dashed lines, Figure 22 shows correct matching of signal pair lengths with serpentine sections to maintain the correct impedance.


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## Layout Example (continued)

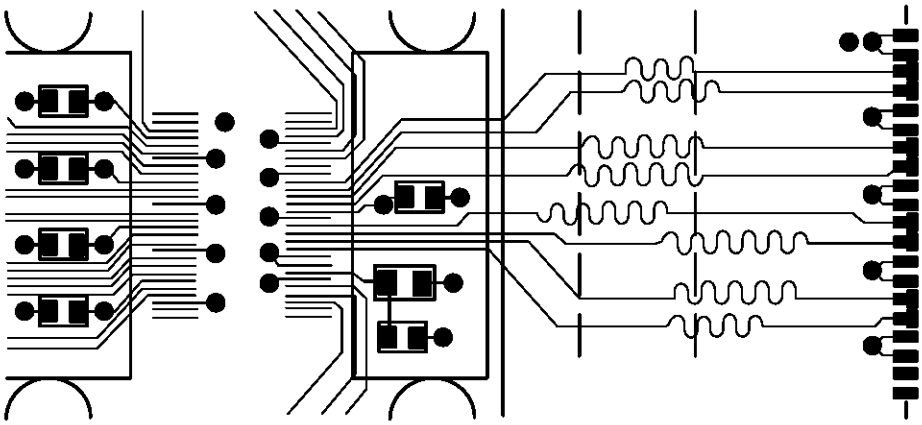


**Figure 22. Mitering LVDS Traces to Match Lengths**

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# 11 デバイスおよびドキュメントのサポート

## 11.1 デバイス・サポート

### 11.1.1 デバイスの項目表記

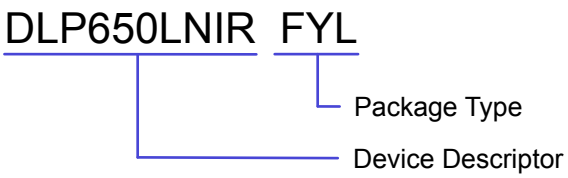



**図 23. 型番の説明**

### 11.1.2 デバイスのマーキング

デバイスのマーキングには、人間が読める情報と2次元マトリクス・コードの両方を使用しています。人間が読める情報を図 24に示します。2次元のマトリクス・コードは英数字の文字列で、DMD型番、シリアル番号のパート1、シリアル番号のパート2が含まれます。DMDシリアル番号（パート1）の最初の文字は製造年です。DMDシリアル番号（パート1）の2番目の文字は製造月です。

例: DLP650LNIRFYL GHXXXXX LLLLLLM

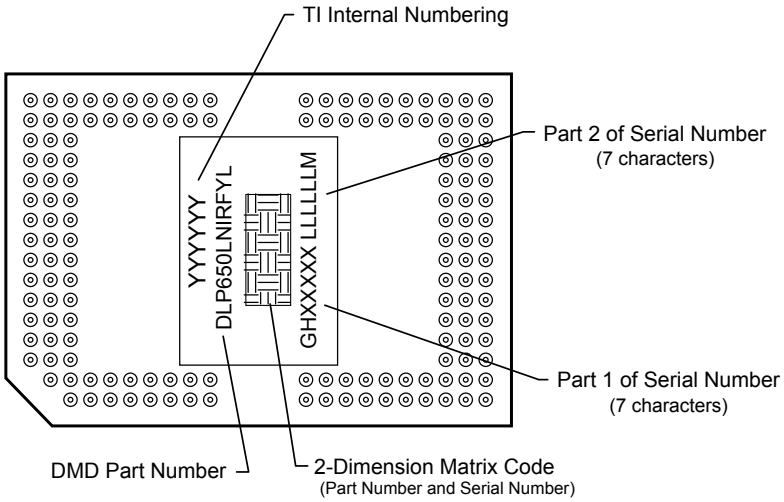



**図 24. DMDのマーキング位置**

## 11.2 ドキュメントのサポート

### 11.2.1 関連資料

次のドキュメントには、DLP650LNIRと組み合わせて使用されるチップセット・コンポーネントに関する追加情報が記載されています。

- 『DLPC410 デジタル・コントローラ』データシート
- 『DLPR410 構成PROM』データシート
- 『DLPA200 DMDマイクロミラー・ドライバ』データシート


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## 11.3 関連リンク

次の表に、クイック・アクセス・リンクを示します。カテゴリには、技術資料、サポートおよびコミュニティ・リソース、ツールとソフトウェア、およびサンプル注文またはご購入へのクイック・アクセスが含まれます。

**表 11. 関連リンク**

| 製品 | プロダクト・フォルダ | サンプルとご購入 | 技術資料 | ツールとソフトウェア | サポートとコミュニティ |
|---|---|---|---|---|---|
| DLP650LNIR | ここをクリック | ここをクリック | ここをクリック | ここをクリック | ここをクリック |
| DLPA200 | ここをクリック | ここをクリック | ここをクリック | ここをクリック | ここをクリック |
| DLPC410 | ここをクリック | ここをクリック | ここをクリック | ここをクリック | ここをクリック |
| DLPR410 | ここをクリック | ここをクリック | ここをクリック | ここをクリック | ここをクリック |

## 11.4 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

## 11.5 コミュニティ・リソース

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**設計サポート** ***TIの設計サポート*** 役に立つE2Eフォーラムや、設計サポート・ ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。

## 11.6 商標

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## 11.8 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

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# 12 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。


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## PACKAGING INFORMATION

| Orderable part number | Status (1) | Material type (2) | Package \| Pins | Package qty \| Carrier | RoHS (3) | Lead finish/ Ball material (4) | MSL rating/ Peak reflow (5) | Op temp (°C) | Part marking (6) |
|---|---|---|---|---|---|---|---|---|---|
| DLP650LNIRFYL | Active | Production | CLGA (FYL) \| 149 | 33 \| JEDEC TRAY (5+1) | Yes | NIPDAU | N/A for Pkg Type | 0 to 70 | |
| DLP650LNIRFYL.B | Active | Production | CLGA (FYL) \| 149 | 33 \| JEDEC TRAY (5+1) | Yes | NIPDAU | N/A for Pkg Type | 0 to 70 | |

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

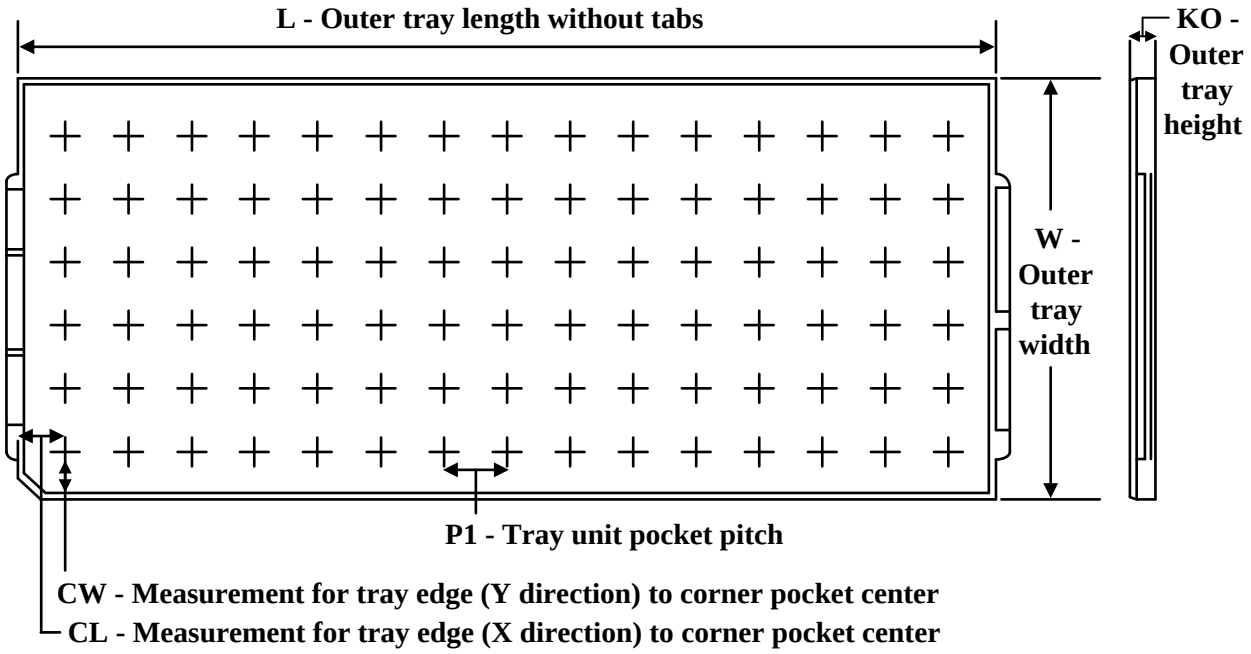
(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TRAY




Chamfer on Tray corner indicates Pin 1 orientation of packed units.

*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | Unit array matrix | Max temperature (°C) | L (mm) | W (mm) | K0 (µm) | P1 (mm) | CL (mm) | CW (mm) |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| DLP650LNIRFYL | FYL | CLGA | 149 | 33 | 3 x 11 | 150 | 315 | 135.9 | 12190 | 27.5 | 20 | 27.45 |
| DLP650LNIRFYL.B | FYL | CLGA | 149 | 33 | 3 x 11 | 150 | 315 | 135.9 | 12190 | 27.5 | 20 | 27.45 |

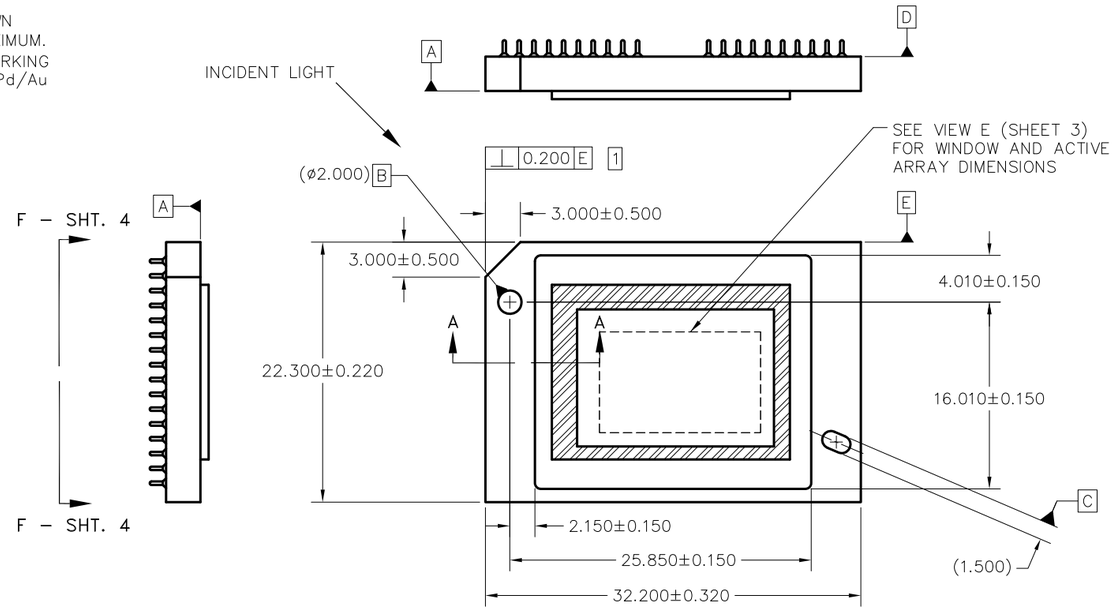
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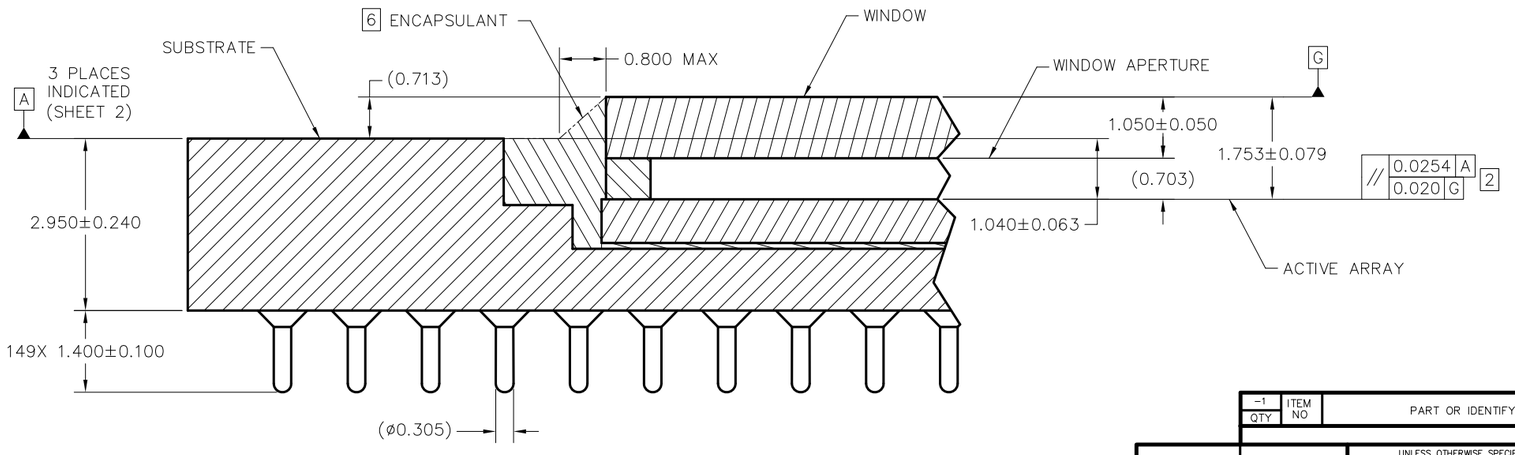
DWG NO 2512372 SH 1

| REVISIONS | | | |
|---|---|---|---|
| REV | DESCRIPTION | DATE | APPROVED |
| A | ECO 2022283, INITIAL RELEASE | 02/07/12 | F. ARMSTRONG |
| B | ECO 2123271, CHG TO LARGE SYMBOLIZATION PAD | 03/16/12 | F. ARMSTRONG |
| C | ECO 2135104, ADD NOTE 8 TO SHEETS 1 & 4 | 08/02/13 | F. ARMSTRONG |
| D | ECO 2168423, ADD FYL PACKAGE TO TITLE | 08/17/17 | M. AVERY |

NOTES: UNLESS OTHERWISE SPECIFIED:

1. SUBSTRATE EDGE PERPENDICULARITY TOLERANCE APPLIES TO ENTIRE SURFACE
2. DIE PARALLELISM TOLERANCE APPLIES TO DMD ACTIVE ARRAY ONLY
3. ROTATION ANGLE OF DMD ACTIVE ARRAY IS A REFINEMENT OF THE LOCATION TOLERANCE AND HAS A MAXIMUM ALLOWED VALUE OF 0.8 DEGREES
4. SUBSTRATE SYMBOLIZATION PAD, AND PLATING AT BOTTOM OF DATUMS B AND C HOLES TO BE ELECTRICALLY CONNECTED TO VSS PLANE WITHIN THE SUBSTRATE
5. BOUNDARY MIRRORS SURROUNDING THE DMD ACTIVE AREA
6. MAXIMUM ENCAPSULANT PROFILE SHOWN
7. ENCAPSULANT ALLOWED ON THE SURFACE OF THE CERAMIC IN THE AREA SHOWN IN VIEW B (SHEET 2). ENCAPSULANT SHALL NOT EXCEED 0.200 THICKNESS MAXIMUM.
8. SUBSTRATES PLATED WITH Ni/Au SHALL HAVE THE THREE-DIGIT NUMERICAL MARKING IN THE AREA ABOVE THE SYMBOLIZATION PAD. SUBSTRATES PLATED WITH Ni/Pd/Au SHALL HAVE THE MARKING IN THE AREA BELOW THE SYMBOLIZATION PAD.




SECTION A–A
SCALE 20/1

| –1 QTY | ITEM NO | PART OR IDENTIFYING NUMBER | NOMENCLATURE OR DESCRIPTION | NOTES |
|---|---|---|---|---|

PARTS LIST

UNLESS OTHERWISE SPECIFIED
- DIMENSIONS ARE IN MILLIMETERS
- TOLERANCES: ANGLES ± 1°
  2 PLACE DECIMALS ±0.25
  3 PLACE DECIMALS ±0.50
- REMOVE ALL BURRS AND SHARP EDGES
- INTERPRET DIMENSIONS IN ACCORDANCE WITH ASME Y14.5–1994
- DIMENSIONAL LIMITS APPLY BEFORE PROCESSES
- PARENTHETICAL INFO FOR REF ONLY

| NEXT ASSY | USED ON |
|---|---|
| NONE | 0314DA |

APPLICATION

THIRD ANGLE PROJECTION

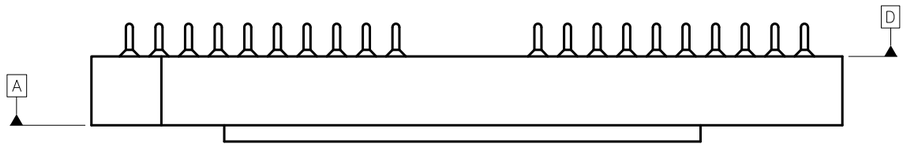
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ENGR F. ARMSTRONG 02/07/12
QA P. KONRAD
CQE M. DORAK

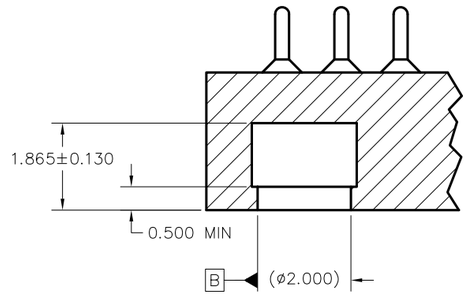
TEXAS INSTRUMENTS
Dallas, Texas

# ICD, MECHANICAL, DMD .65 WXGA–800 2xLVDS V2 SERIES 450 (FYL PACKAGE)

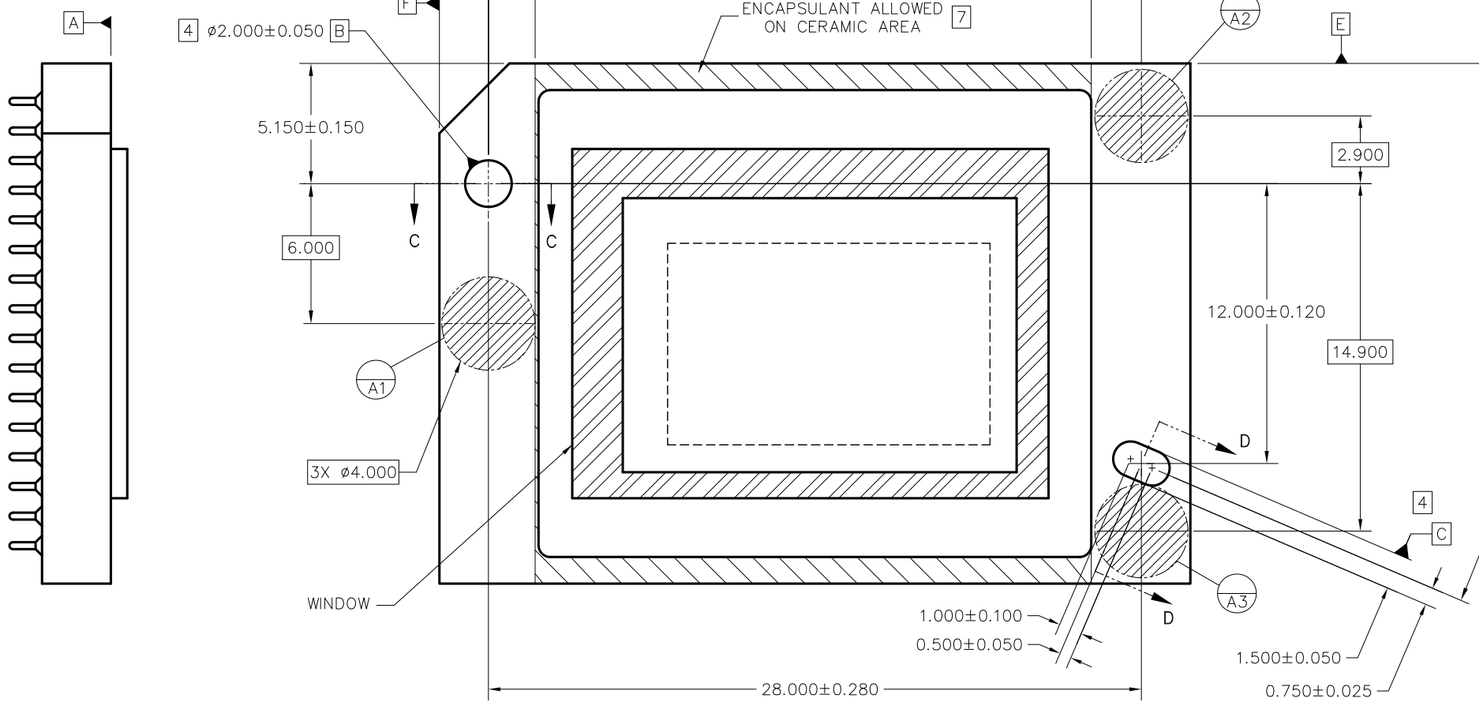
SIZE D | DRAWING NO 2512372 | REV D
SCALE 4/1 | SHEET 1 OF 4

ACED1g

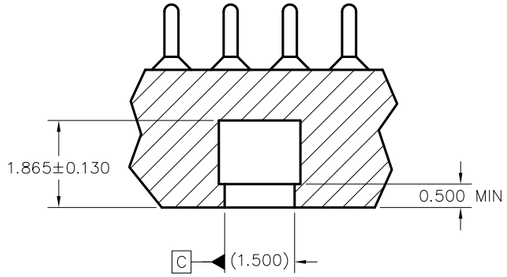



SECTION C–C
DATUM B
SCALE 16/1



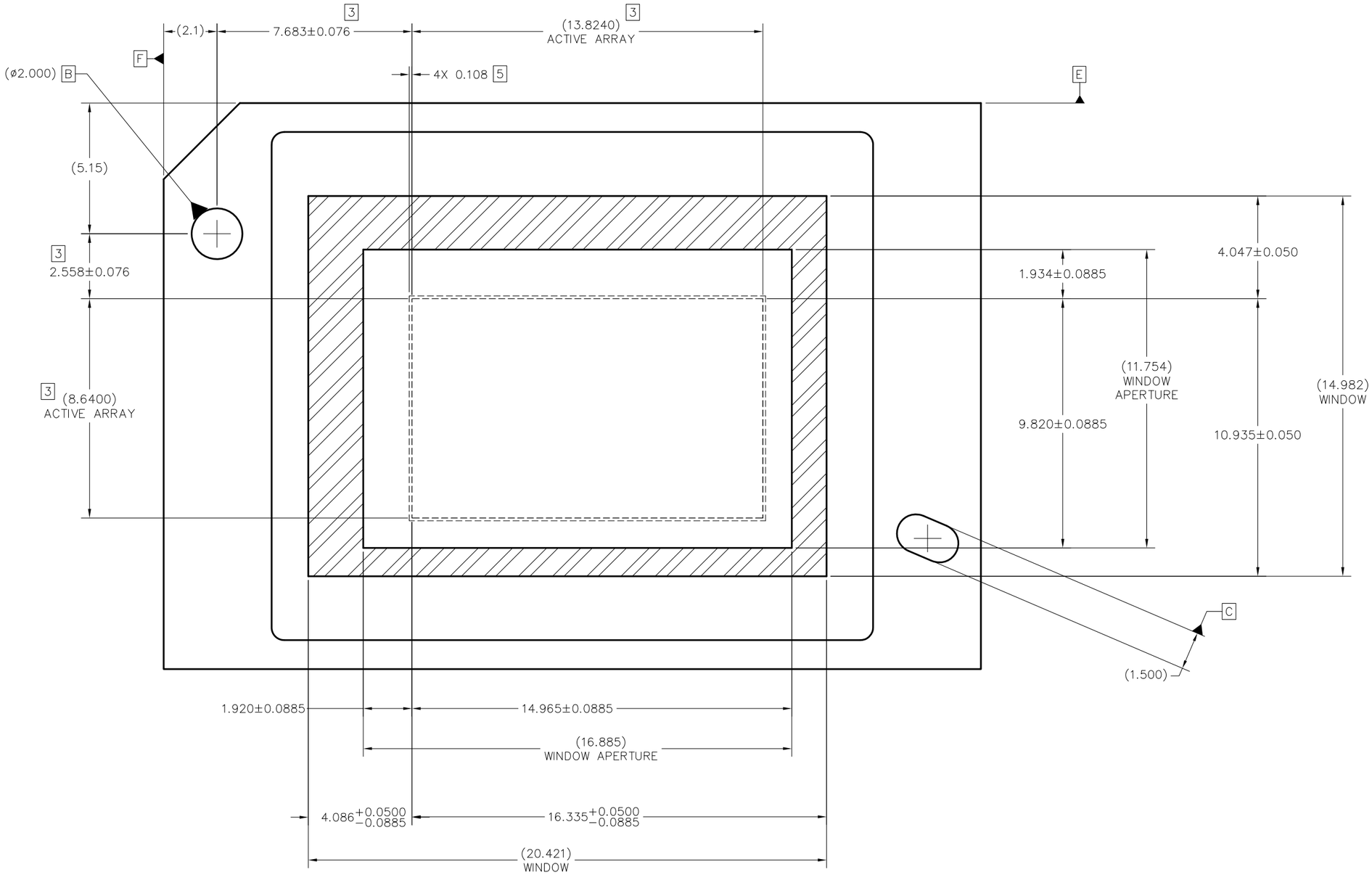

VIEW B
DATUMS AND ENCAPSULANT ALLOWABLE AREA
SCALE 8/1




SECTION D–D
DATUM C
SCALE 16/1

| | | | | |
|---|---|---|---|---|
| TEXAS INSTRUMENTS Dallas, Texas | DWN DATE / ISSUE DATE | SIZE D | DRAWING NO 2512372 | REV D |
| | | SCALE 4/1 | SHEET 2 | |

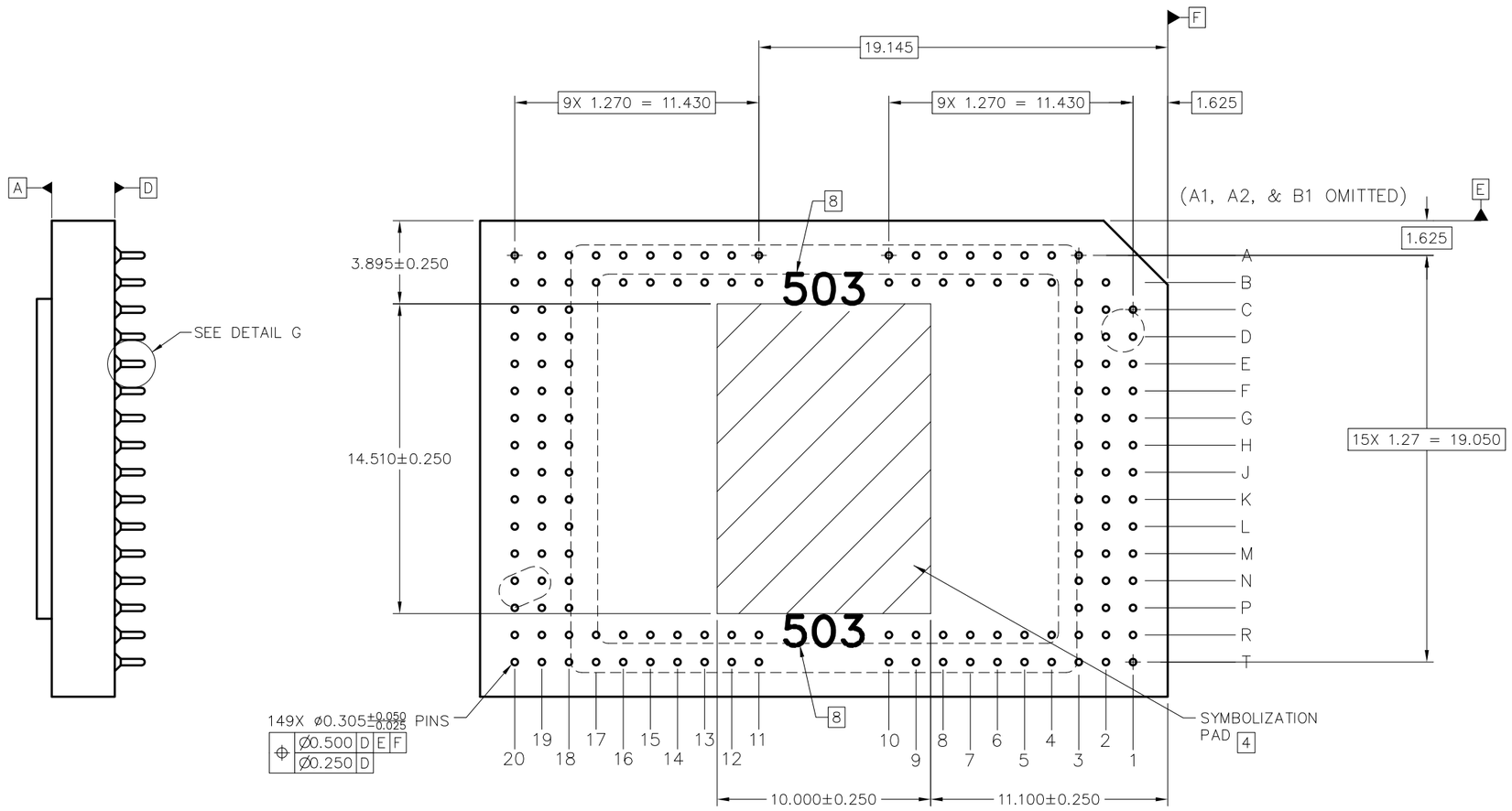
ACED2c



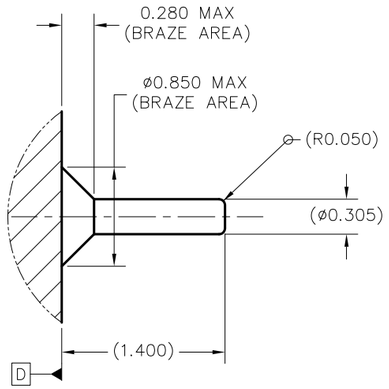

VIEW E (SHEET 1)
DMD WINDOW AND ACTIVE ARRAY
SCALE 12:1

| | | | | | |
|---|---|---|---|---|---|
| Texas Instruments, Dallas, Texas | DWN DATE | SIZE D | DRAWING NO 2512372 | REV D |
| | ISSUE DATE | SCALE 4/1 | SHEET 3 | |

ACED2c




VIEW F–F (SHEET 1)
PINS AND SYMBOLIZATION PAD
SCALE 8/1




DETAIL G (149 PLACES)
PIN & BRAZE DIMENSIONS
SCALE 40/1

| | | | |
|---|---|---|---|
| Texas Instruments, Dallas, Texas | DWN / DATE | SIZE D | DRAWING NO 2512372 REV D |
| | ISSUE DATE | SCALE 4/1 | SHEET 4 |

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